



A High Eta Forward Muon Trigger & Tracking detector for CMS

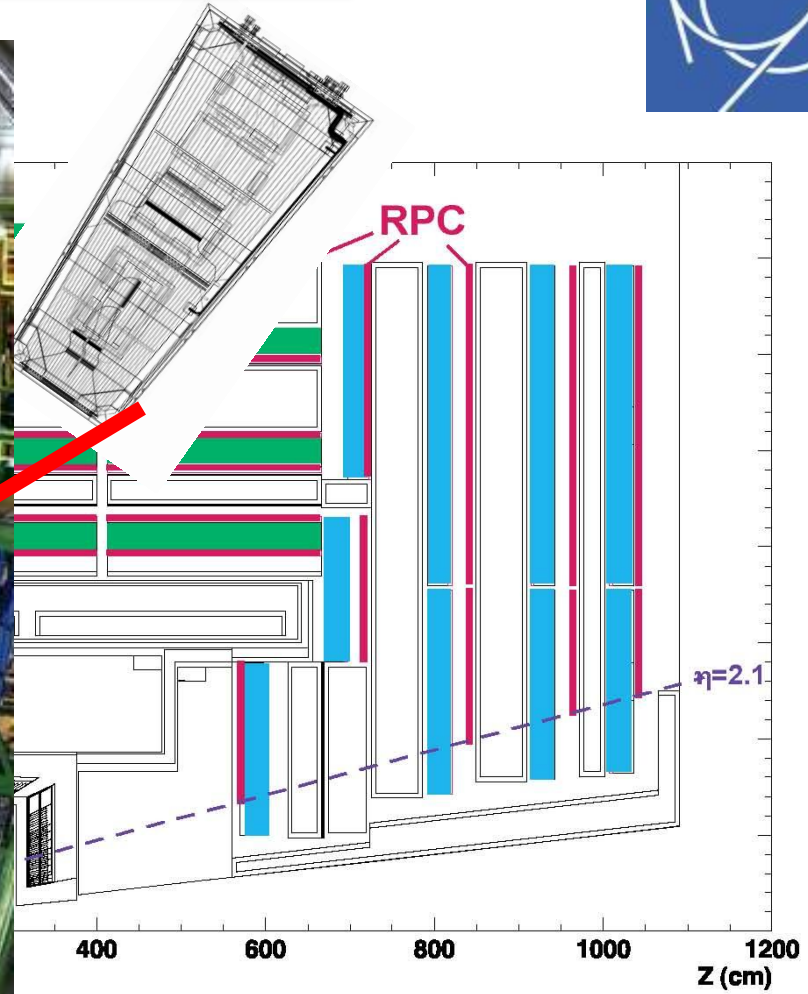
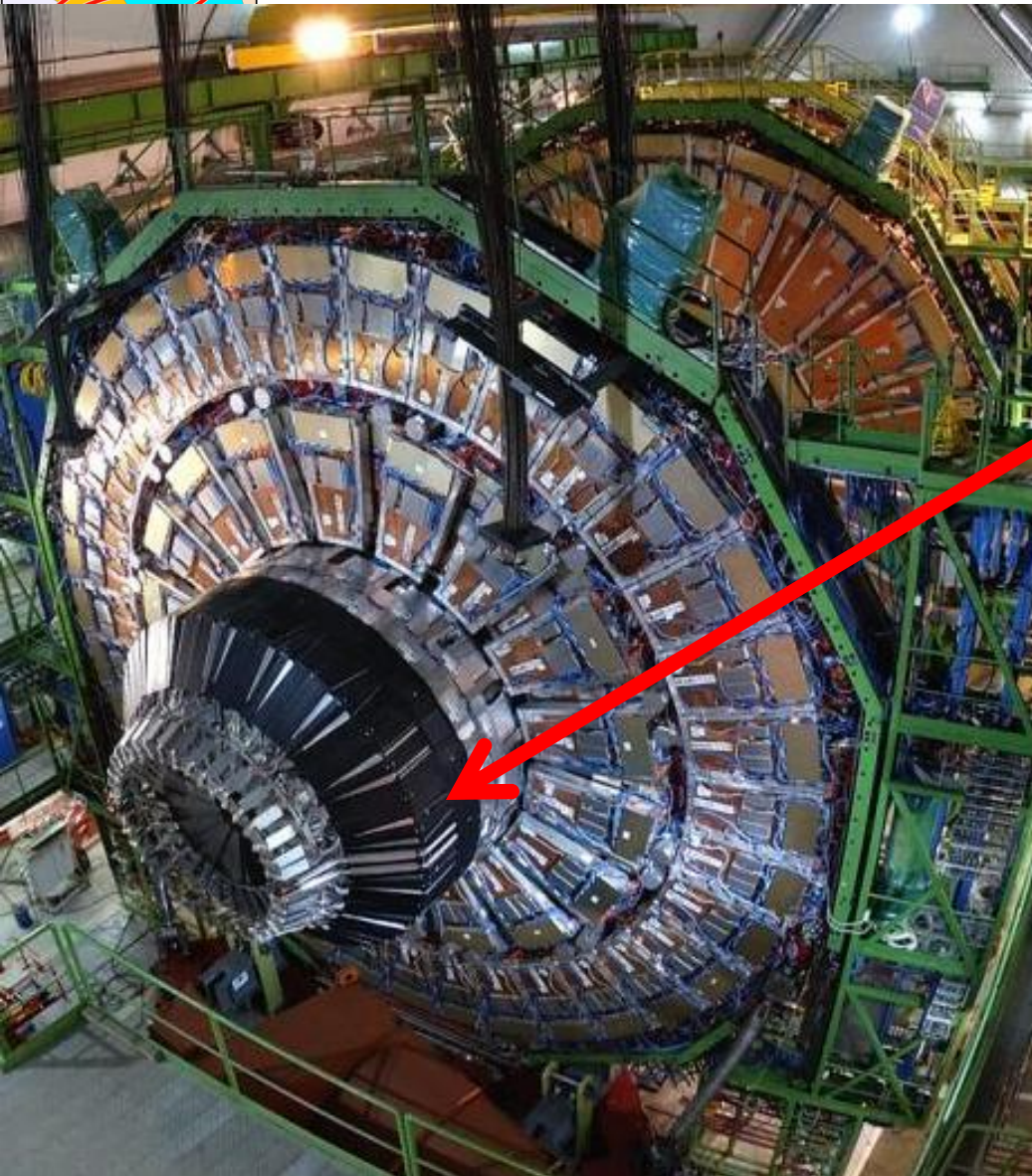
PROTO GE1/1 – With The Largest GEM Foils

UPDATE AT RD51 COLLABORATION MEETING BARI

Archana Sharma

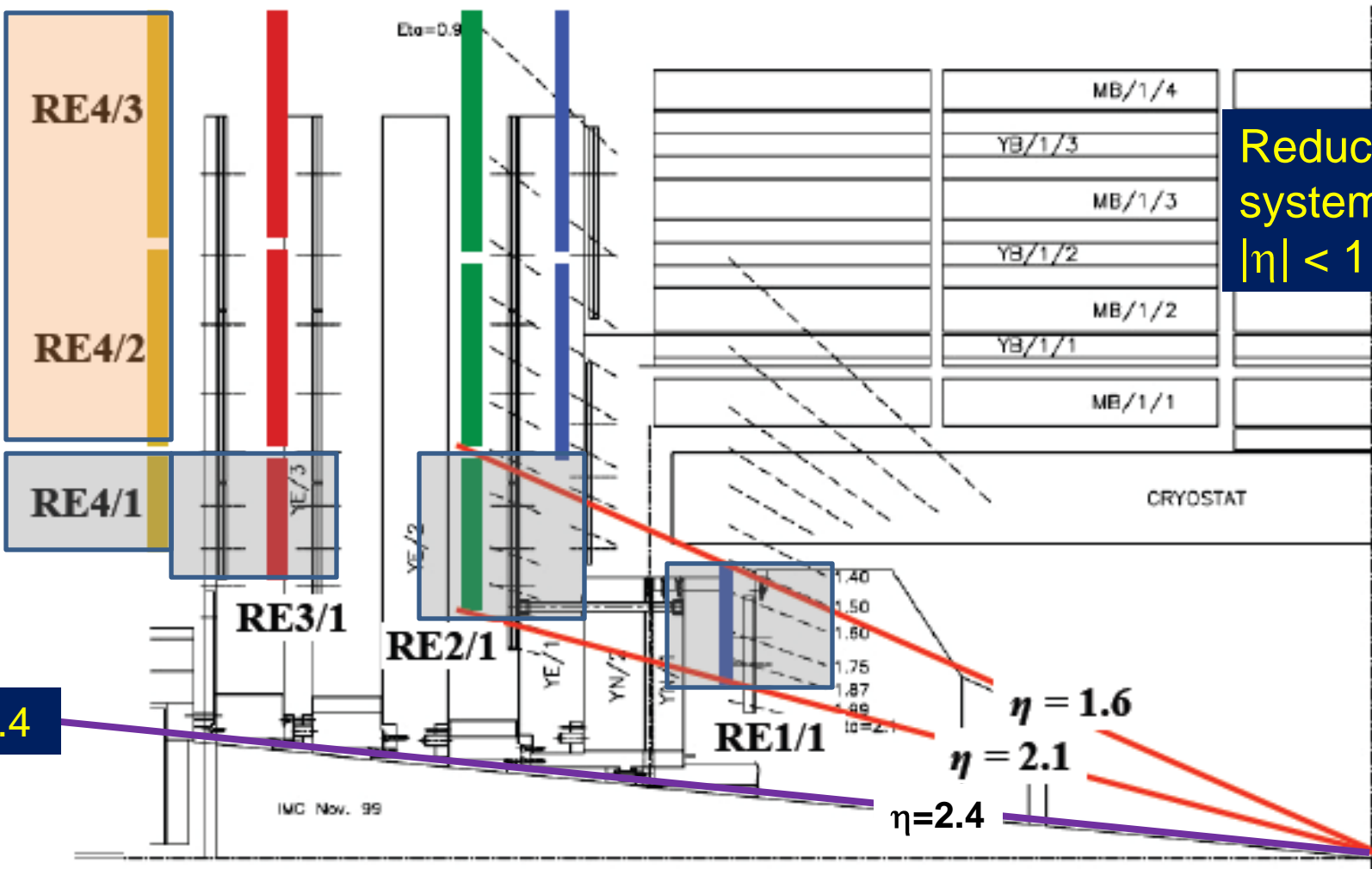
For CMS High Eta Upgrade Team
CMS GDD RD51

Oct 8-11, 2010



- Endcap RPC:
- RE 1,2,3,4 = 1 layers
 - 540 trapezoidal chambers
 - 80 000 radial strips

Initial RE system –tailored to budget



STAGED

	RE 1/1	RE 1/2	RE 1/3	RE 2/1	RE 2/2	RE 2/3	RE 3/1	RE 3/2	RE 3/3	RE 4/1	RE 4/2	RE 4/3
No. of chambers	36*2	36*2	36*2	18*2	36*2	36*2	18*2	36*2	36*2	18*2	36*2	36*

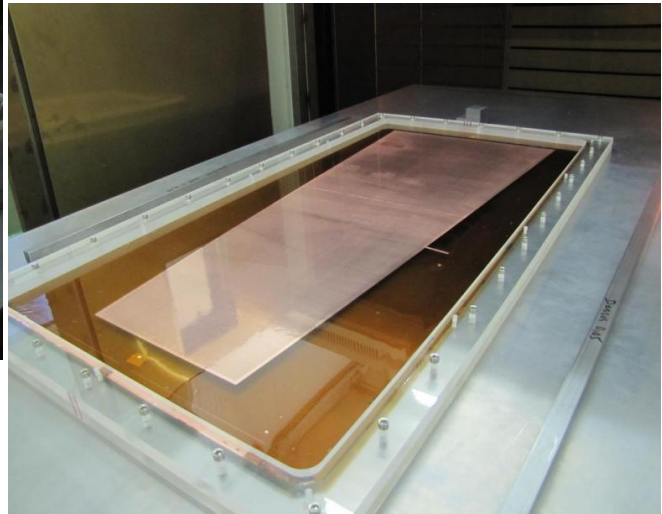
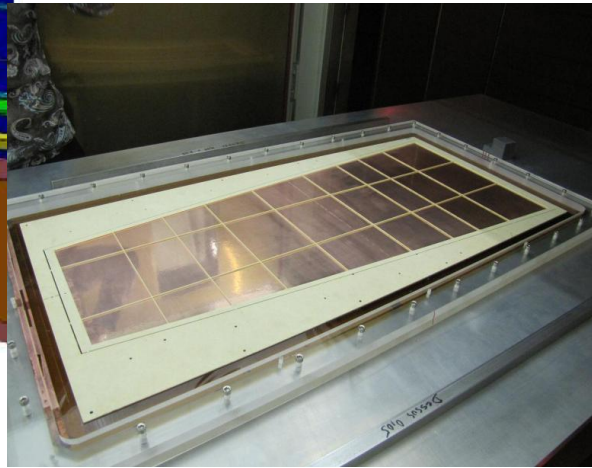
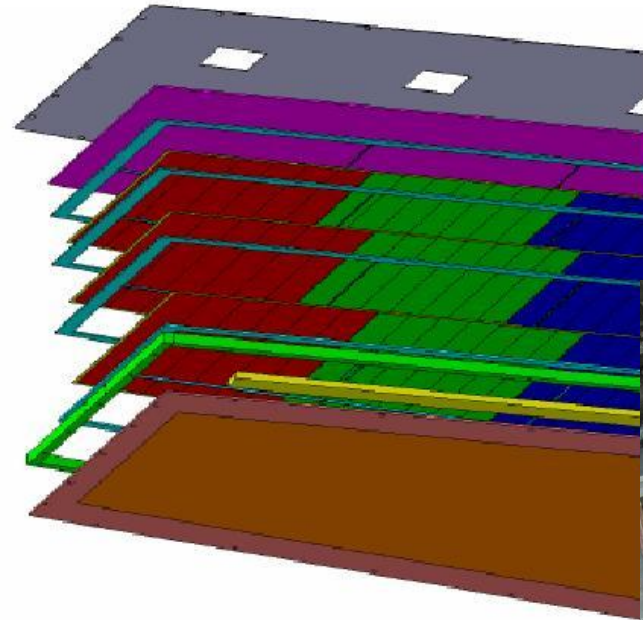


Estimated Particle rates in Forward CMS

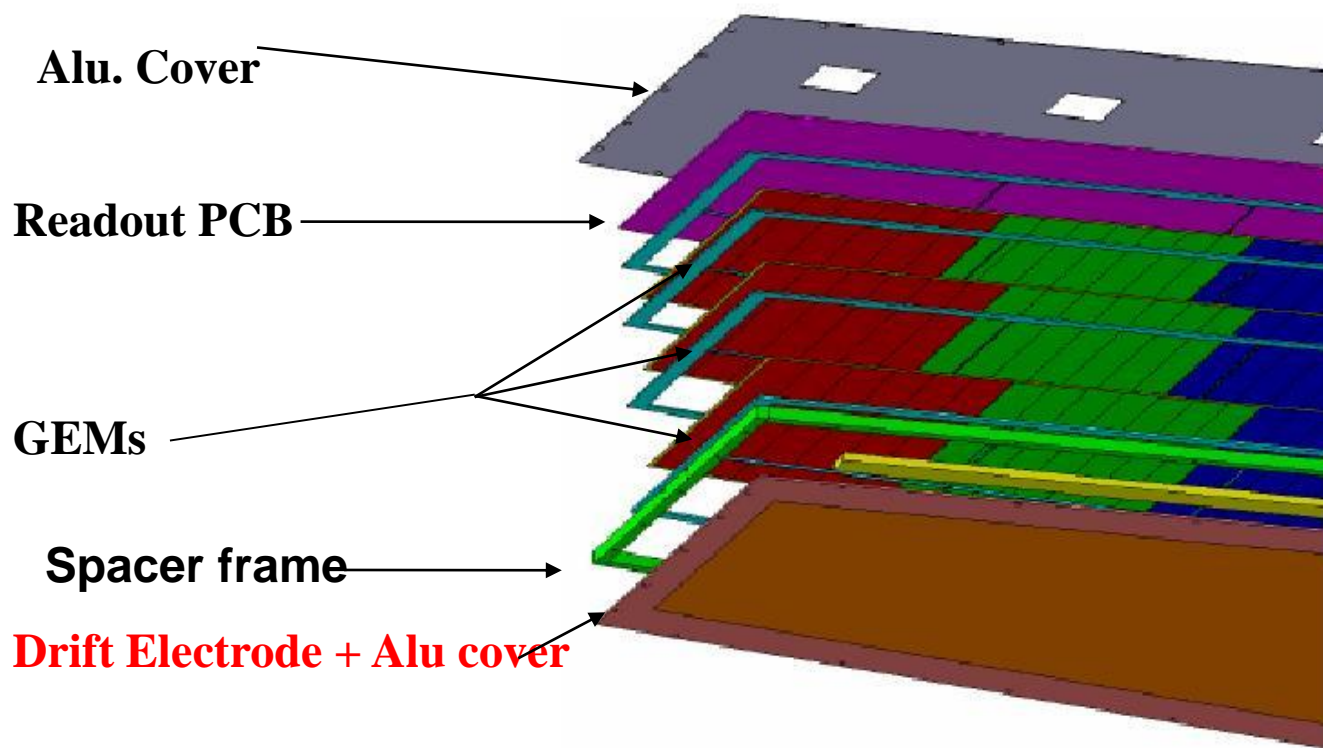


RPC Region	Rates Hz/cm ² LHC (10 ³⁴ cm ² /s)	High Luminosity LHC 2.3 x LHC	(10 ³⁵ cm ² /s) Phase II SLHC ??
RB	30	Few 100	500 Hz - kHz (tbc)
RE 1, 2, 3,4 $\eta < 1.6$	30	Few 100	kHz (tbc)
Expected Charge in 10 years	0.05 C/cm ²	0.15 C/cm ²	~ C/cm ²
RE 1,2,3,4 $\eta > 1.6$	500Hz ~ kHz	Few kHz	Few 10s kHz
Total Expected Charge in 10 years	(0.05- 1) C/cm ²	few C/cm ²	Few 10s C/cm ²

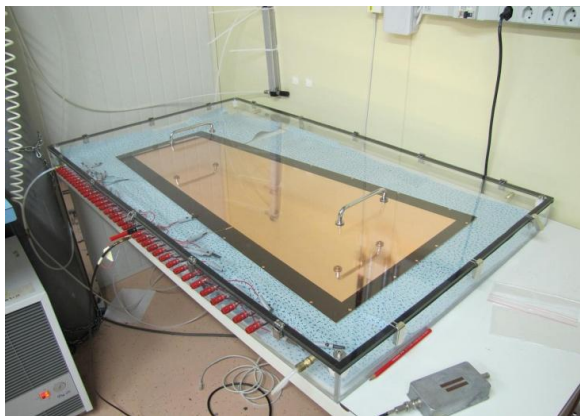
CONSTRUCTION OF THE LARGE PROTOTYPE CMS GE1/1



GE1/1 3D Model



GE1/1 Drift Electrode

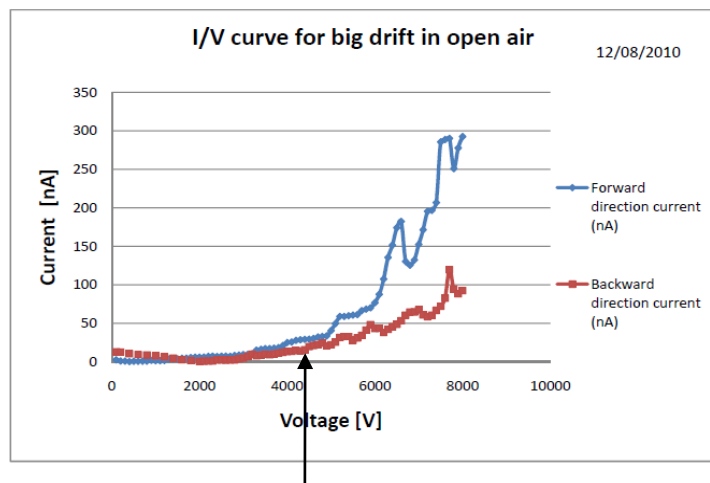


Cu Foil – 5 μ m

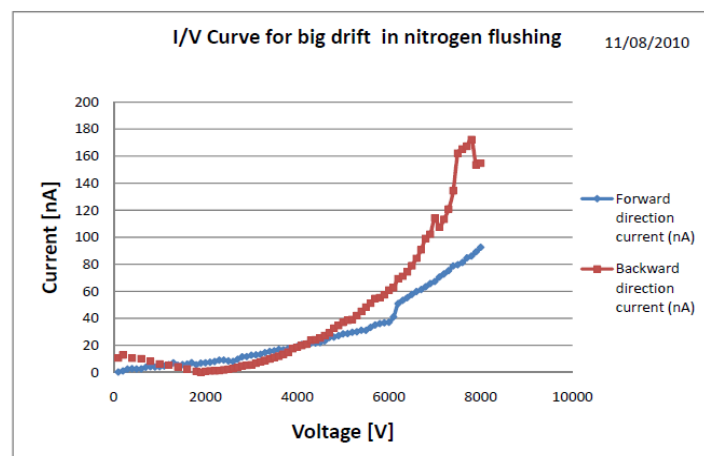
Kapton stack 300 μ m (75 + 100 + 75 + 50)

Aluminum plate 3mm

The operation voltage is 4.5kV
The leakage current is 20nA in open Air

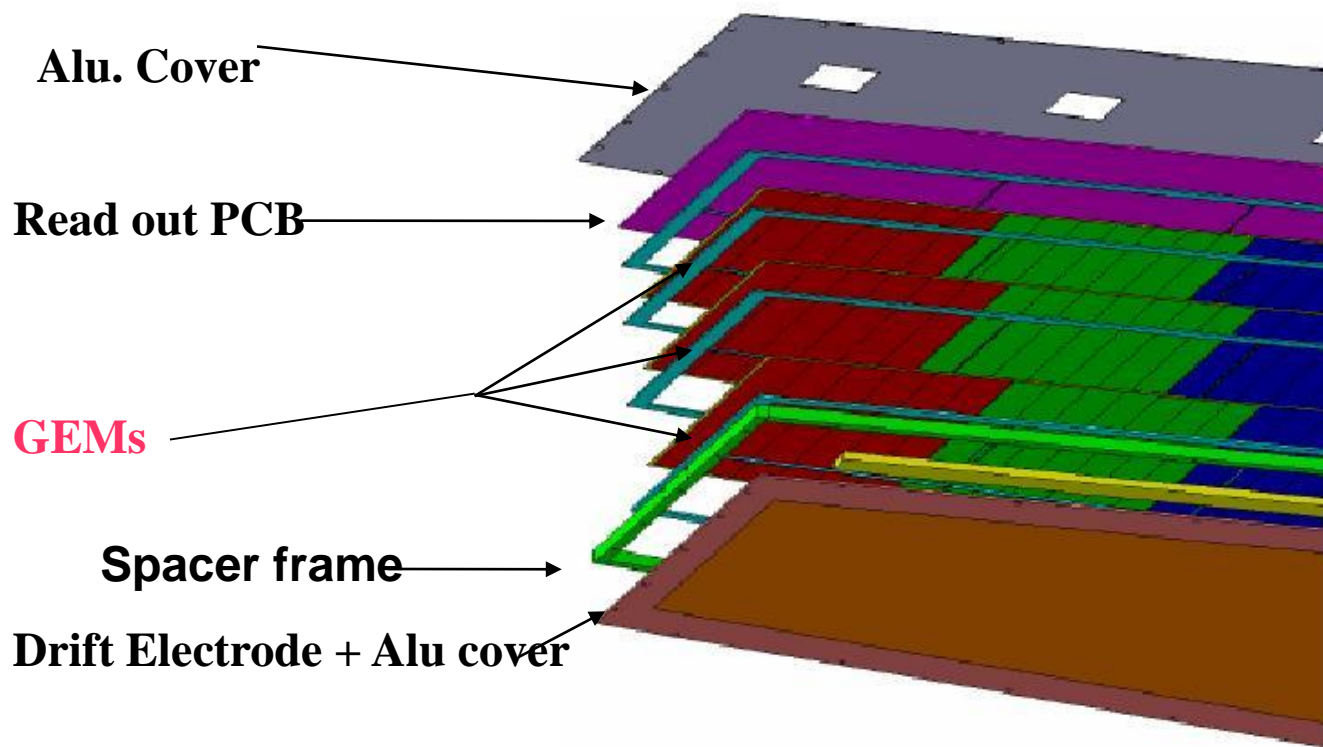


Working point





GE1/1 3D Model

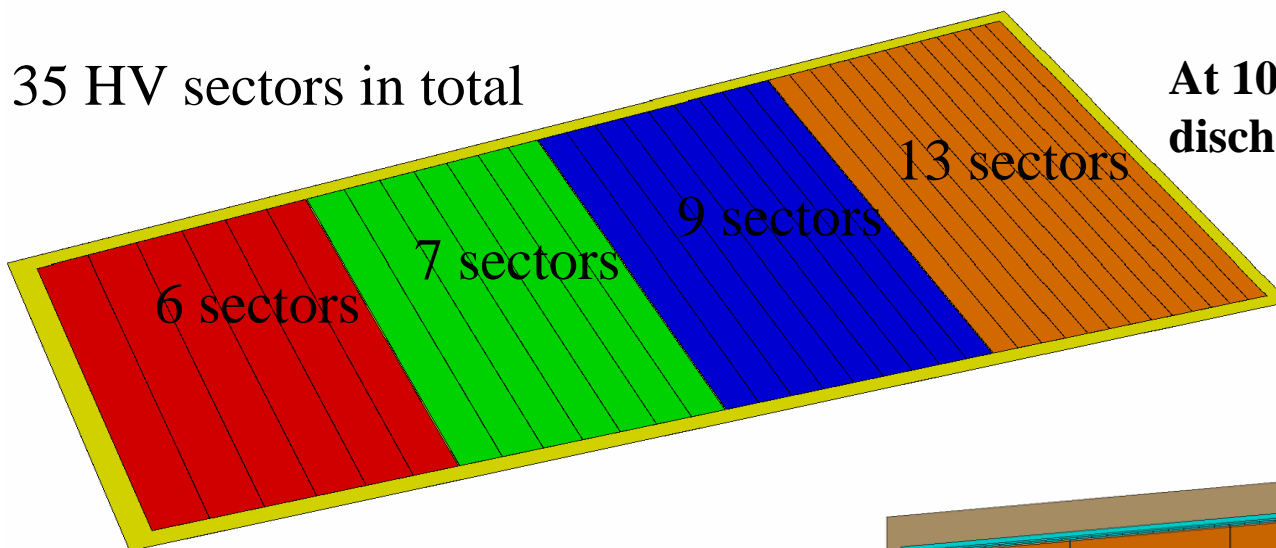




GE1/1 – GEM Foils Sectorization

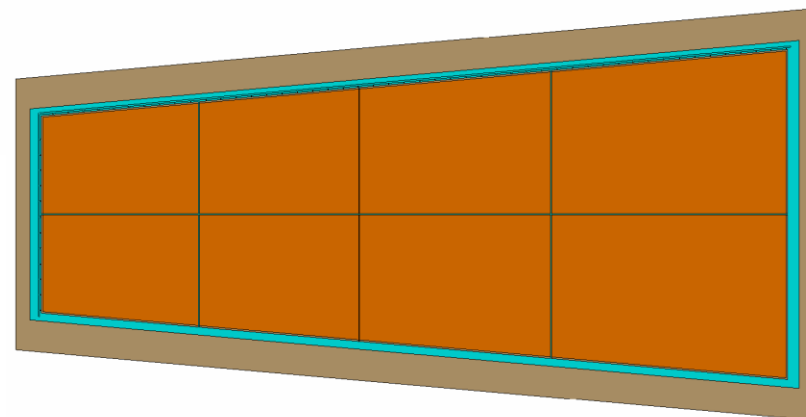
1 HV GEM sector = 100cm²

35 HV sectors in total



At 100cm² the probability of discharge is negligible

4 Eta sectors



Using Single Mask(SM) production technology

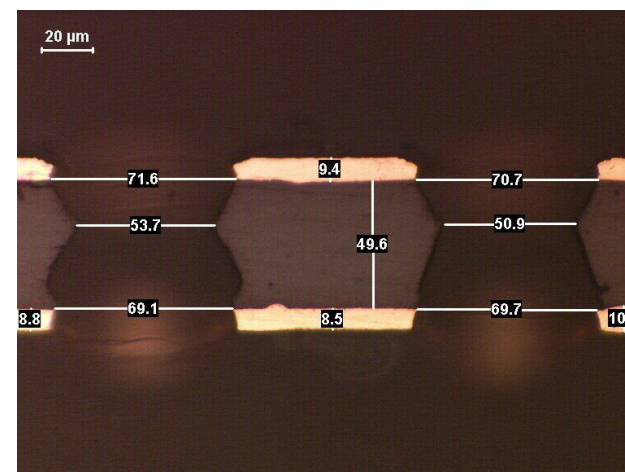
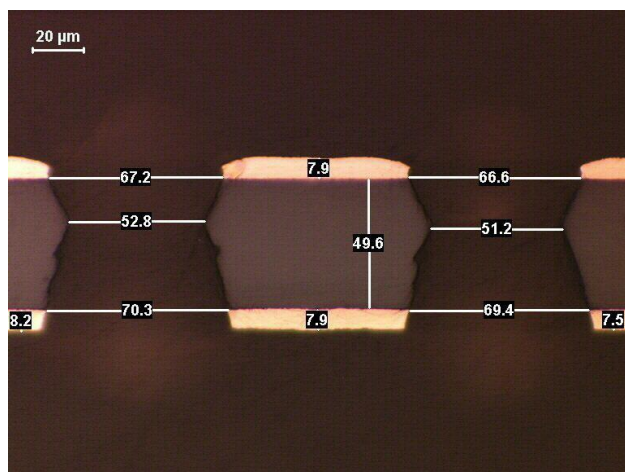
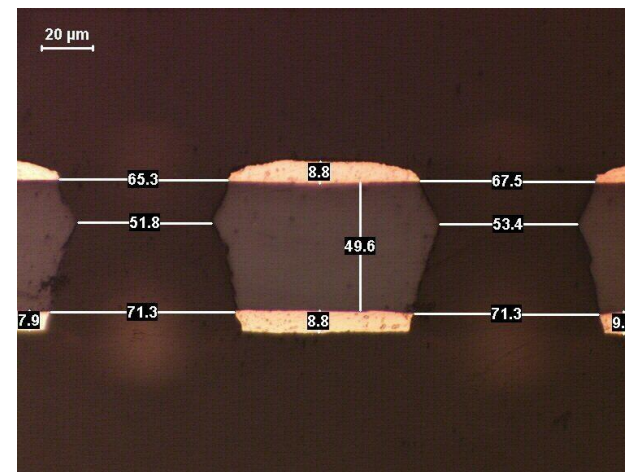
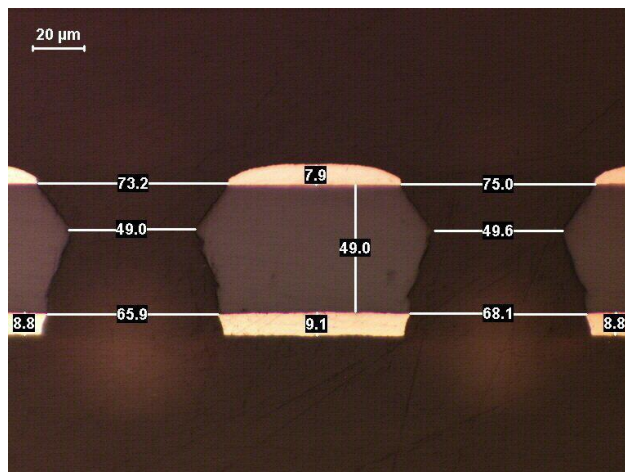
Rui's Workshop builds Largest Sized Single Mask GEMs



CMS: 1m x 45cm (6 pieces)

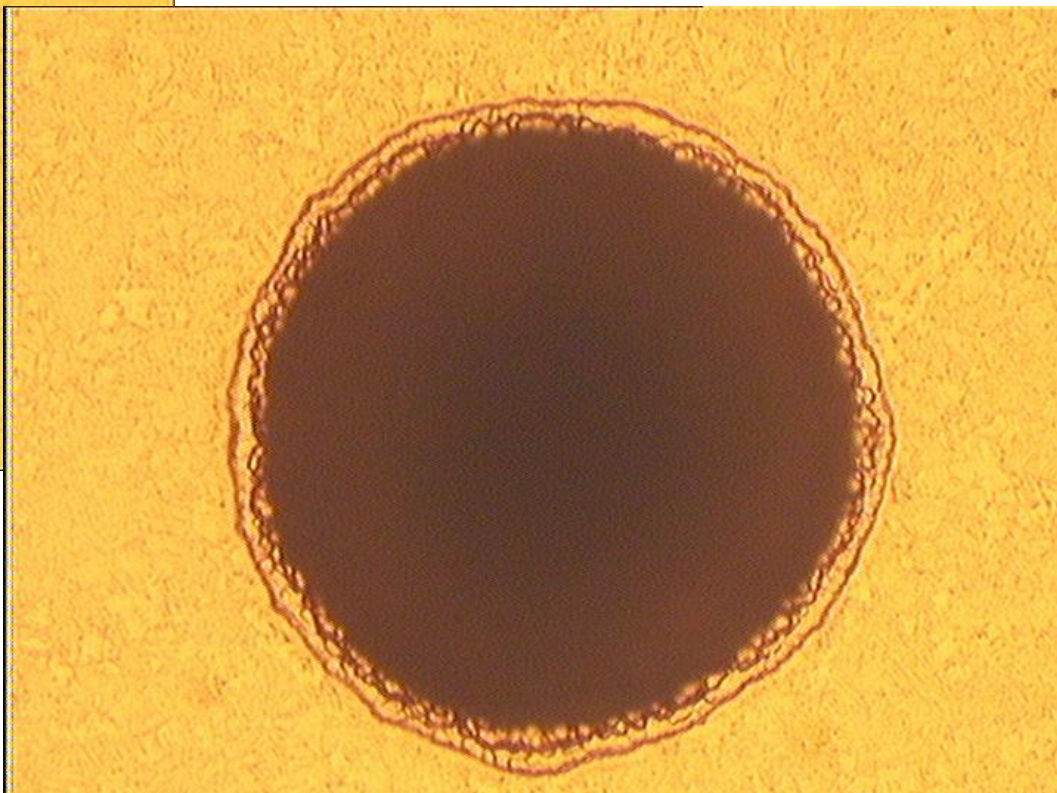
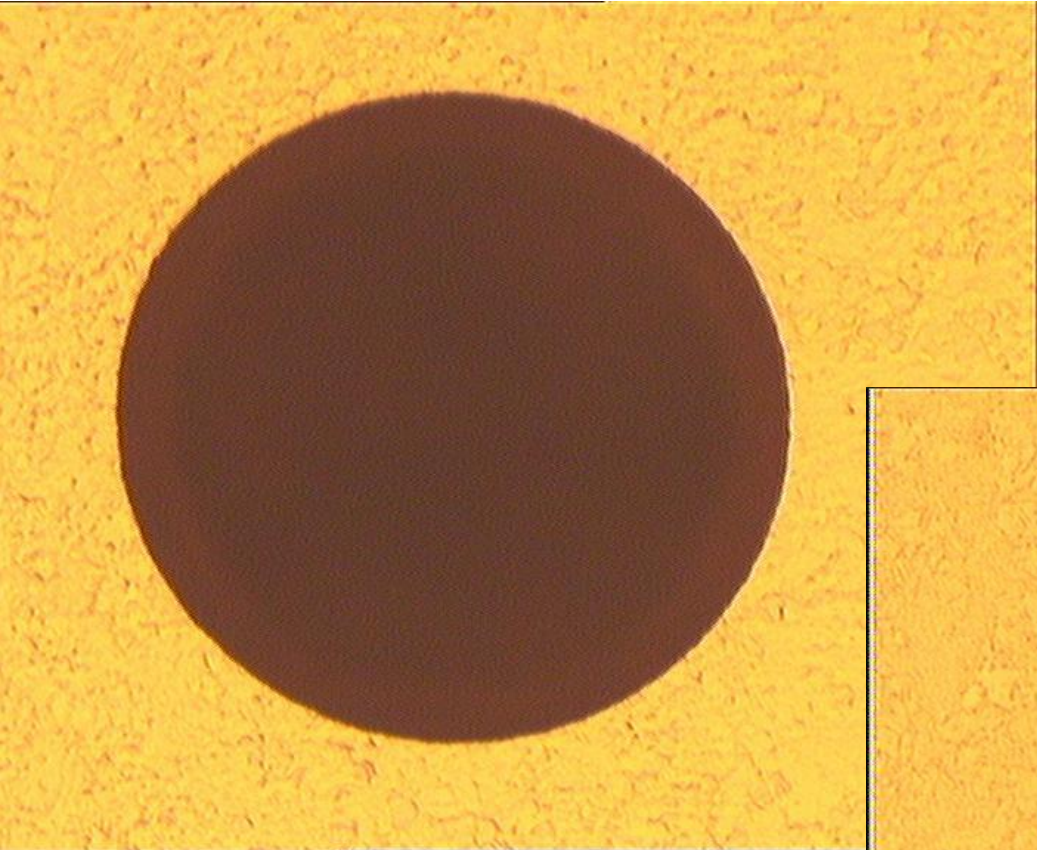


cross section pictures

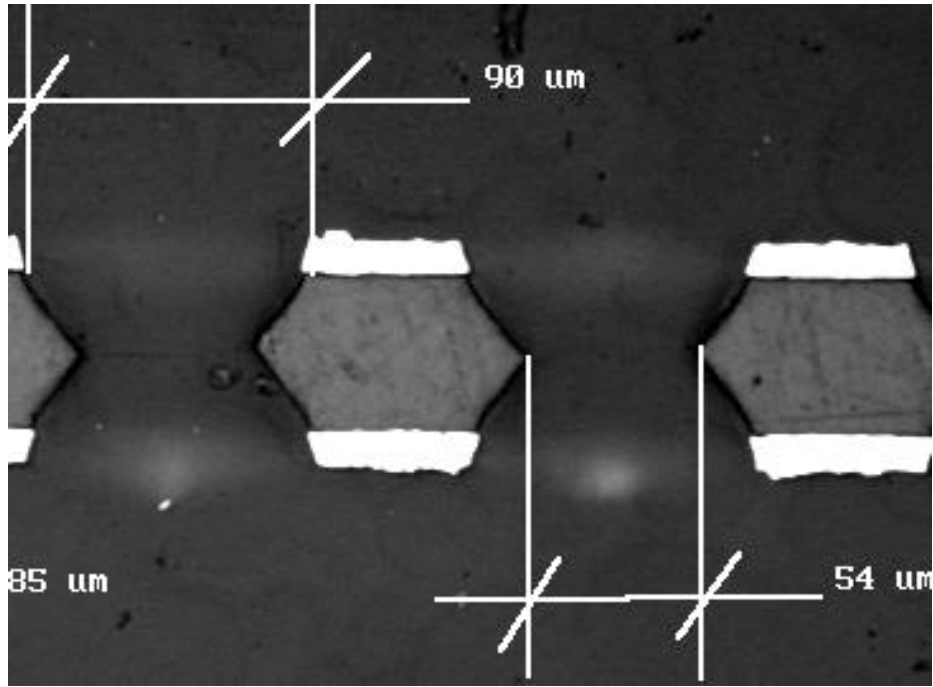
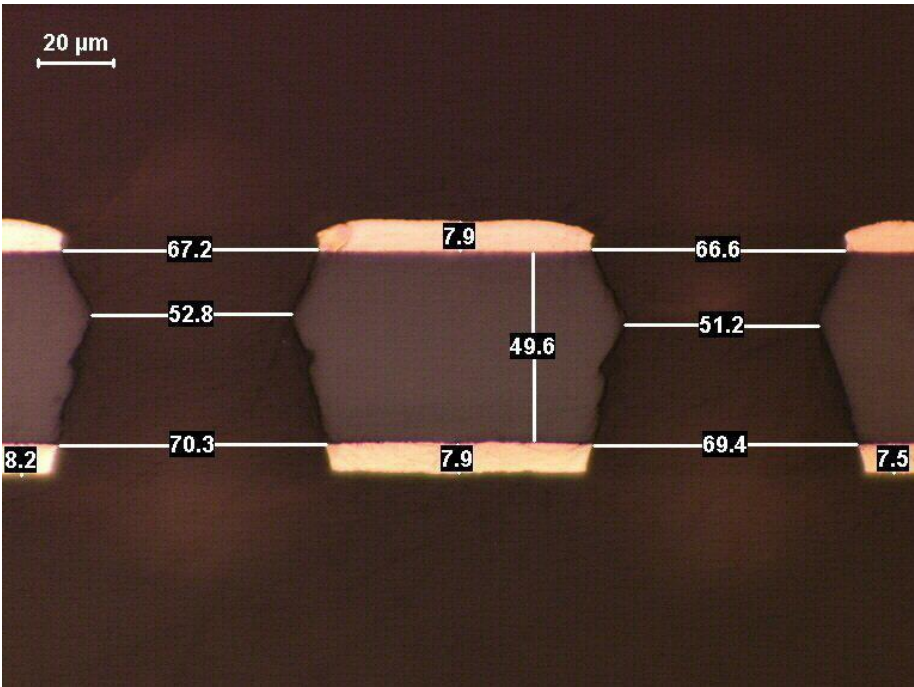




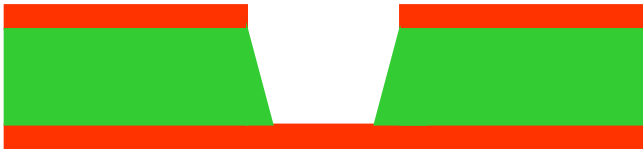
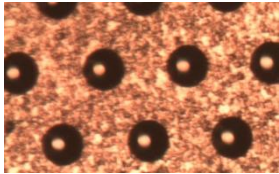
Introducing GEM #3 – electrodes...



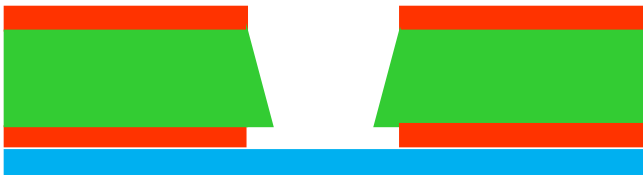
Comparison with *standard GEM* from external supplier



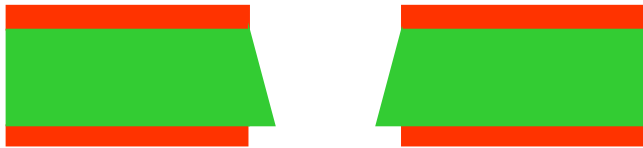
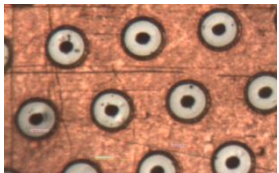
GEM single mask process



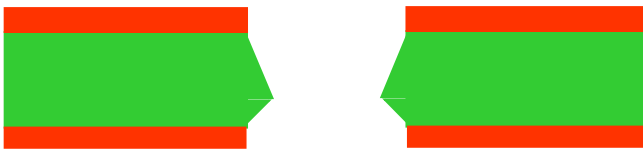
Chemical Polyimide etching



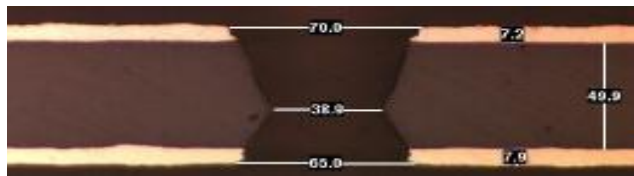
Copper electro etching



Stripping

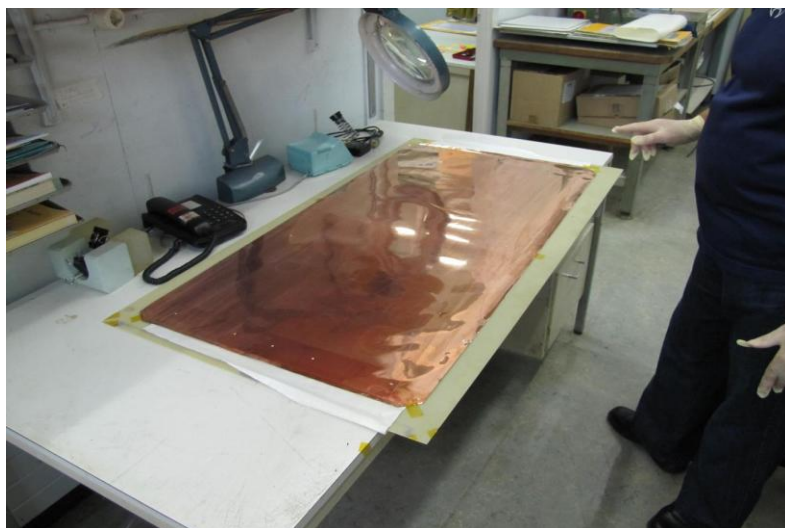
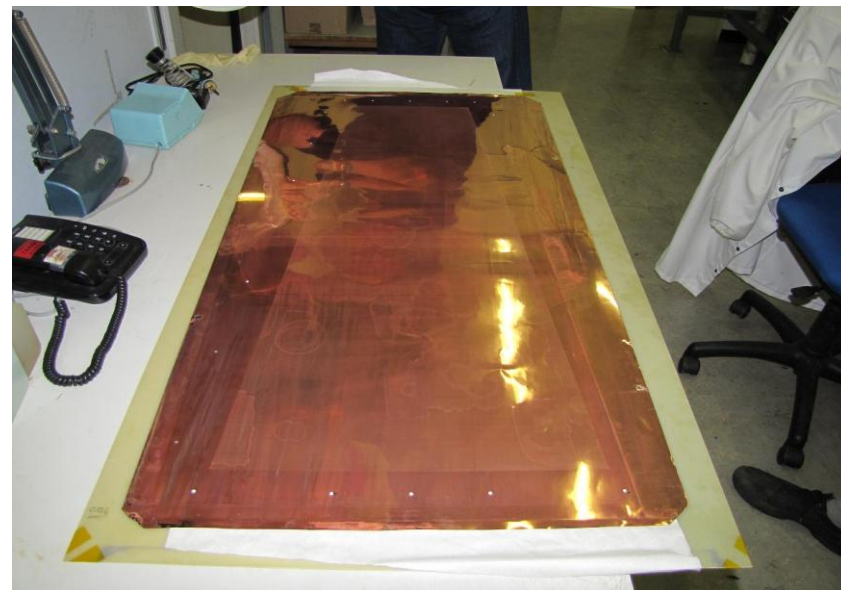
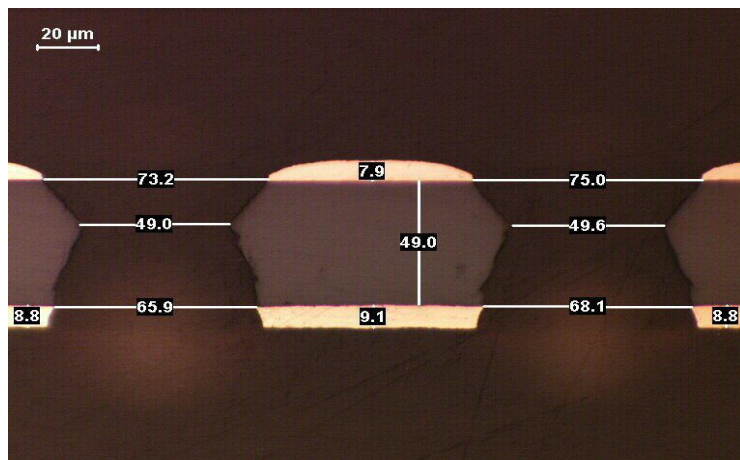


Second Polyimide etching



Reality

Production of CMS Single Mask (SM) GEMs



Single Mask technology
Eliminates
alignment of the holes issue
Size 990/45.5/22 mm

Rui's Workshop

Single Mask GEMs



CMS: 1m x 45cm (6 pieces)

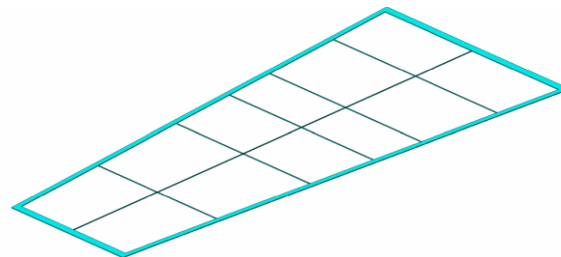
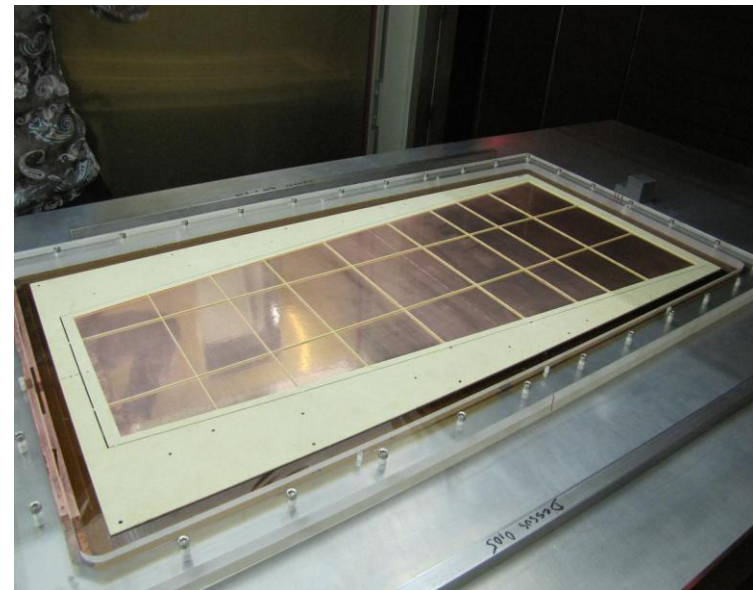
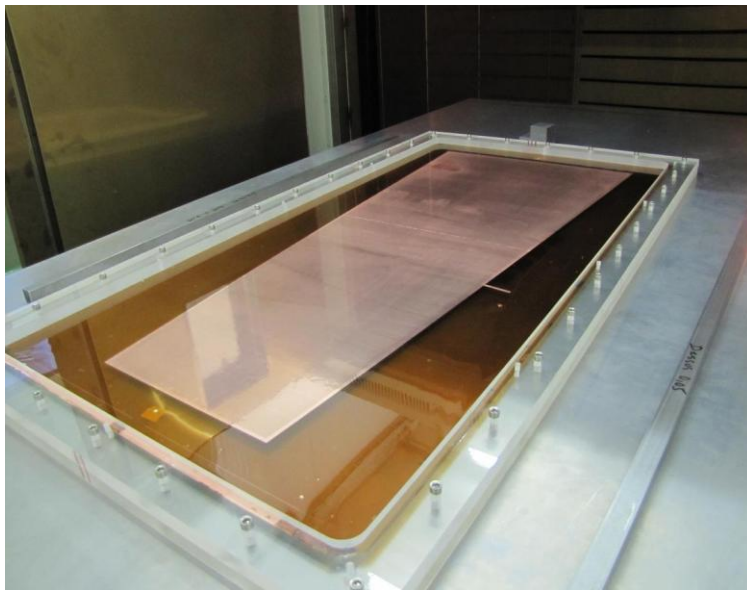


- GEM foil goes in a special oven for heating up to 37degree



Stretching and Framing Procedure for GE1/1 GEMs

- Gluing the spacer frame on the GEM foil.



Stretching and Framing Procedure for GE1/1 GEMs

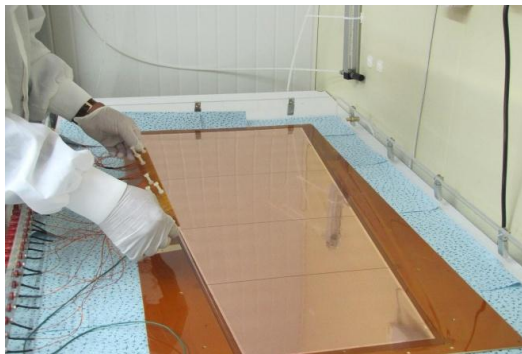
- The GEM foil, with glued frame, stays in the oven heated up to 37°C over 24 hours.



Before and after stretching and framing, the GEMs are passing QT of the GE1/1

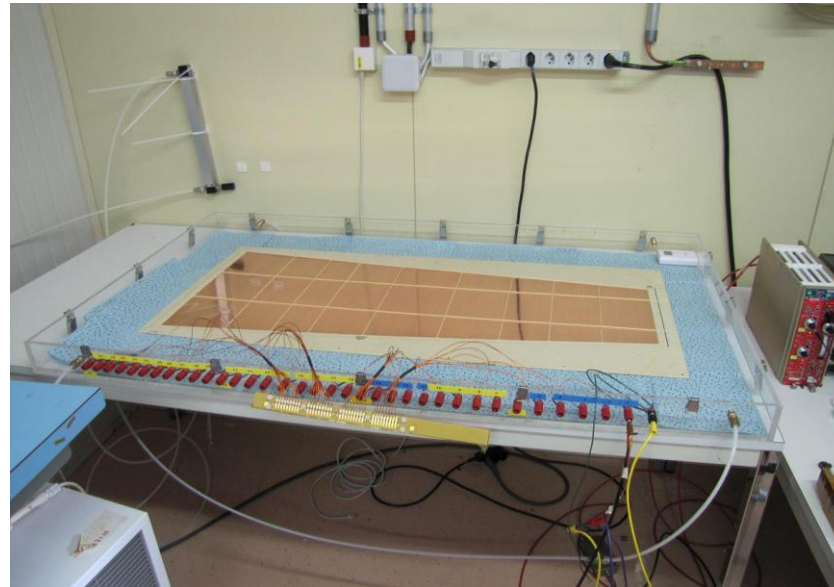
1. Optical inspection
2. HV test before stretching
3. HV test after stretching

→ Applying up to 500V between the top sector and the bottom layer plus the 2 neighbor sectors as well.



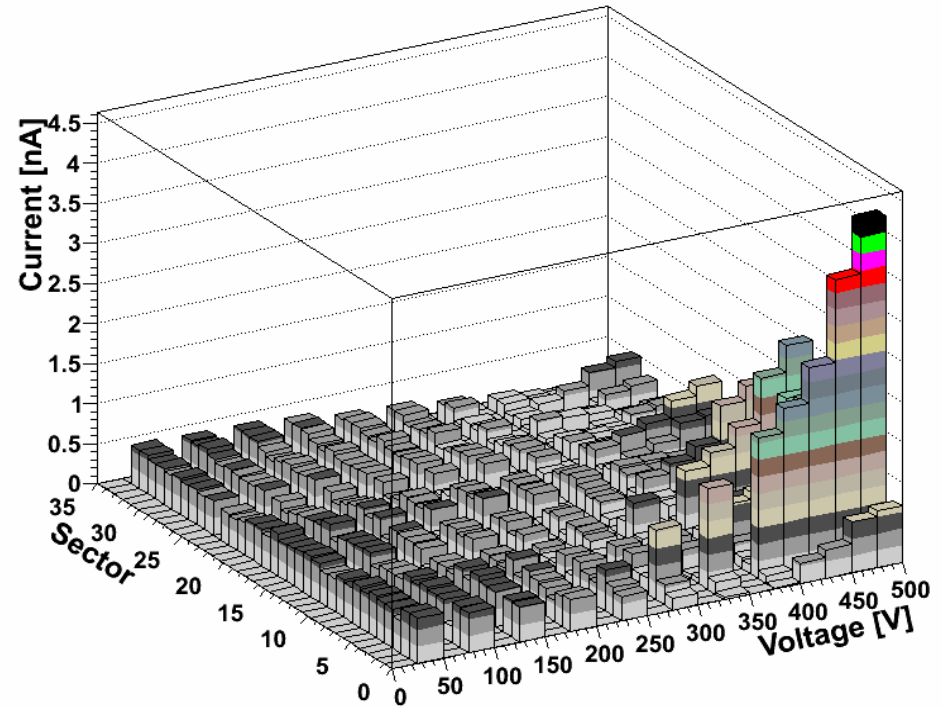
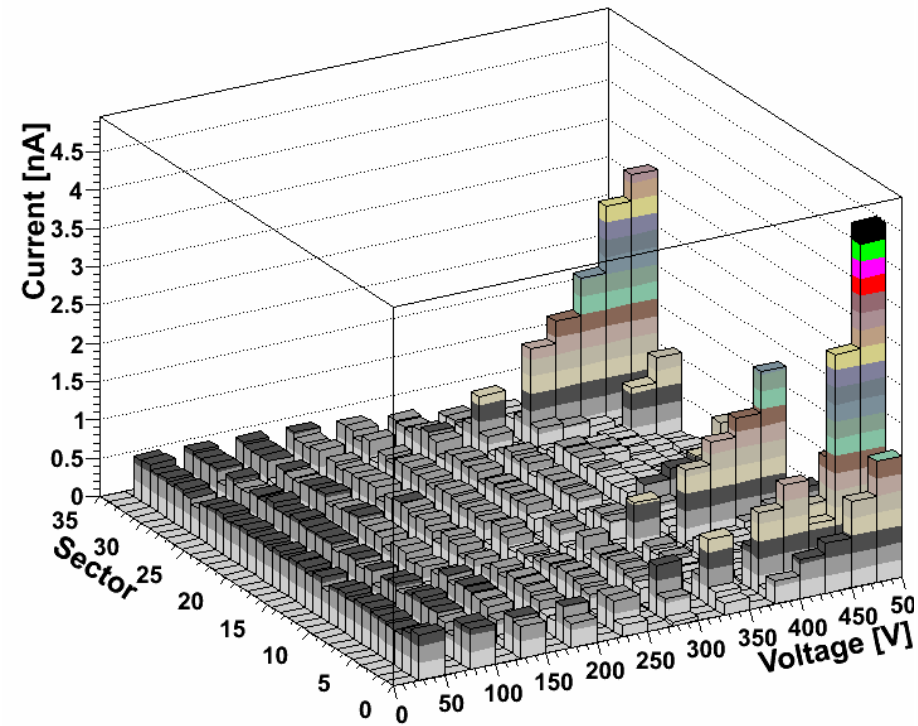
Testing sector by sector

Criteria - Current less 10nA



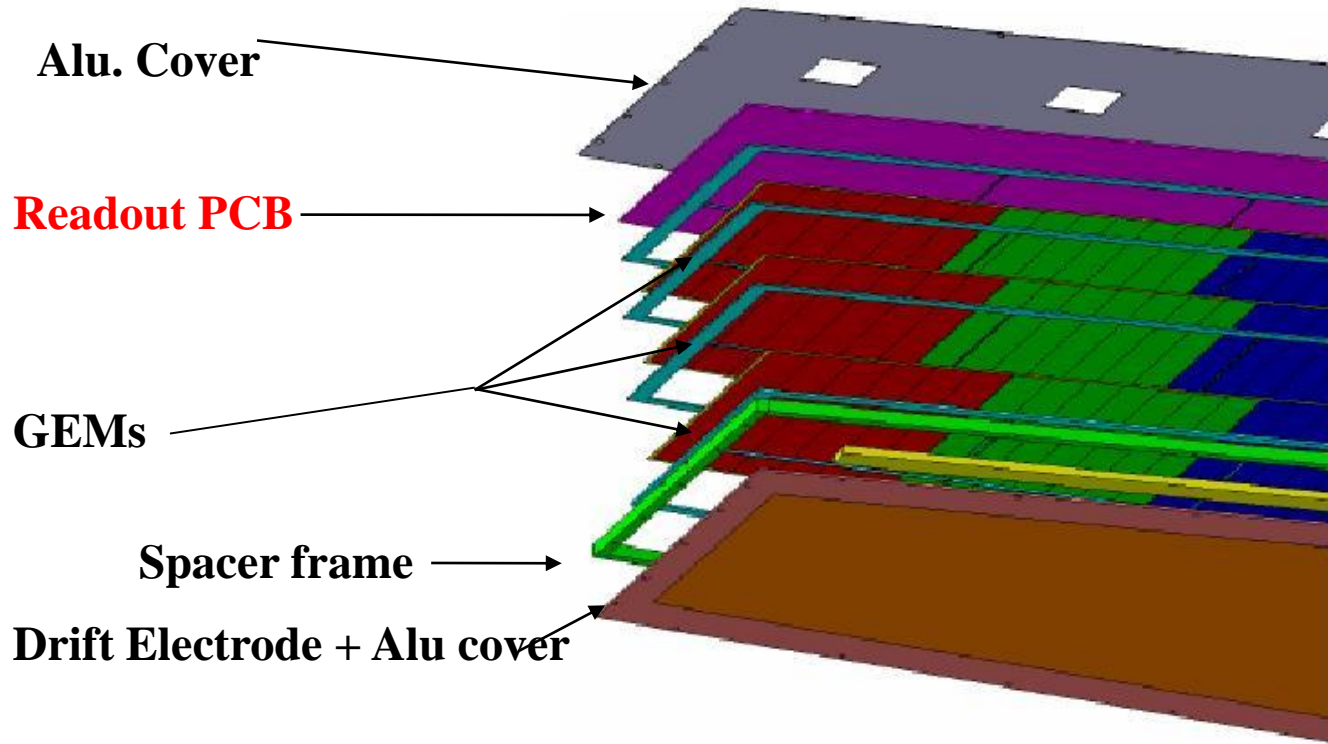
GEM5_Foil

GEM5_Stretche

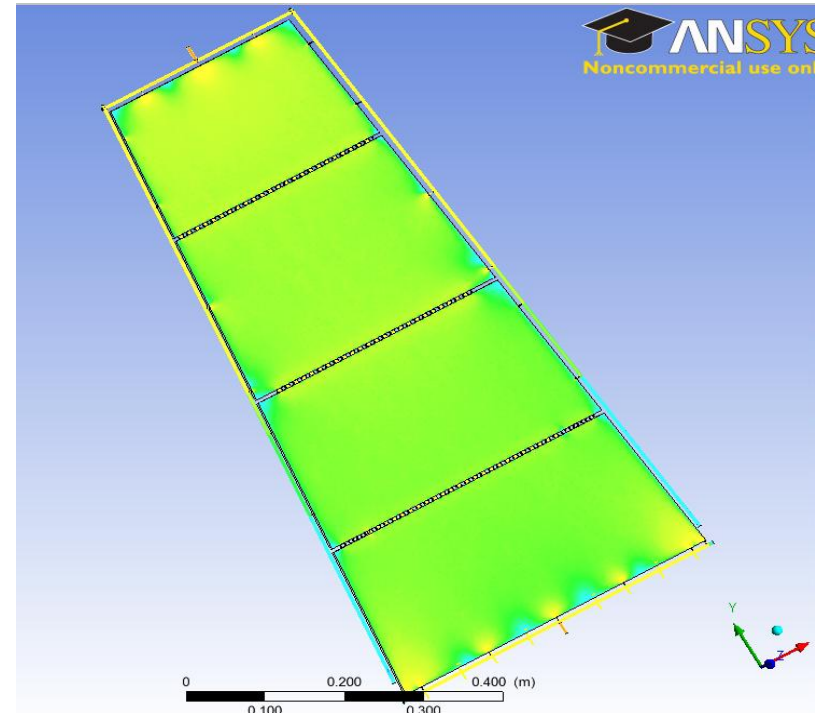


Results of the HV test. Sectors/Voltage/Current

3D Model of GE1/1

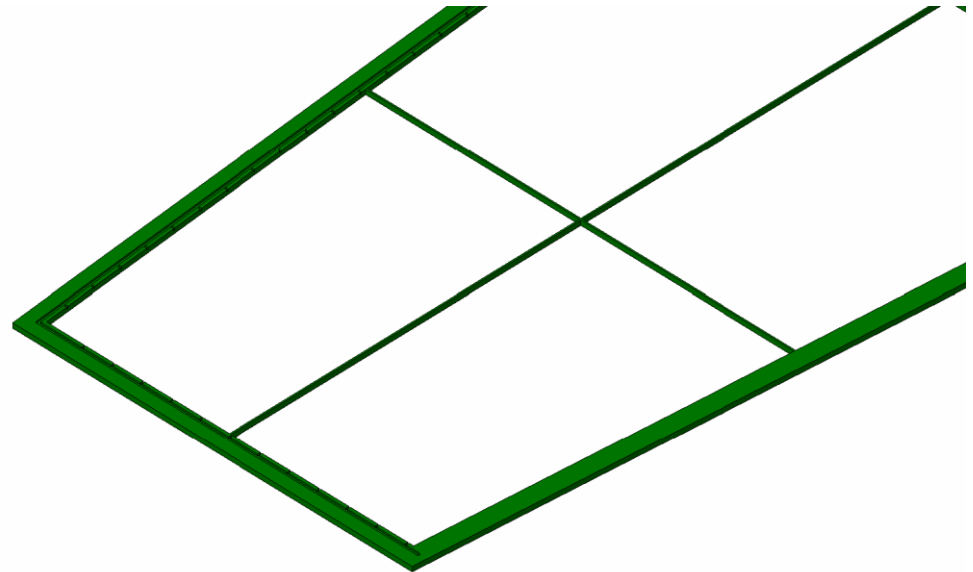
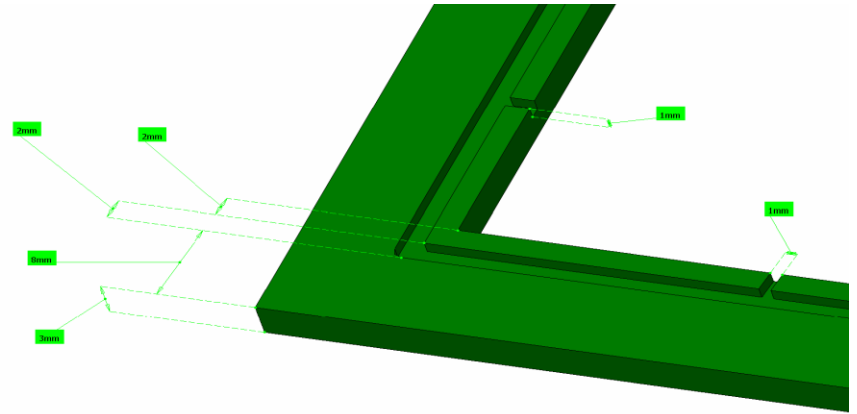


- Gas flow studies and simulation with ANSYS
- Taking in to account all the environmental conditions – gravity, different gas mixtures, temperature, atmospheric pressure
- Gas Mixtures studied
 - Ar-CO₂ 70-30%
 - Ar-CO₂-CF₄ 45-15-40%

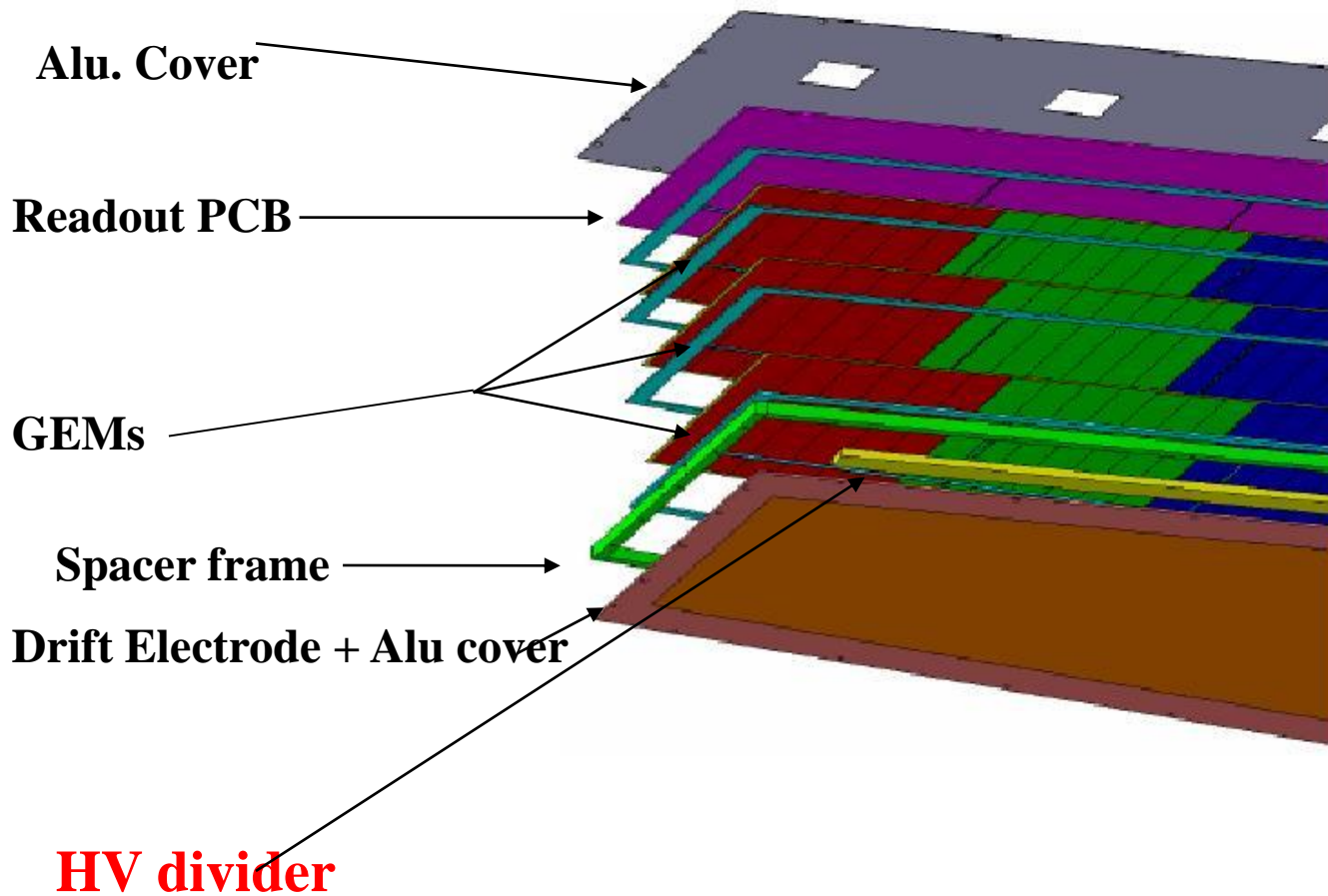


Gas I/O Design

- Based on the simulations we have the optimal gas flow I/O design.
- Minimizing the number and size of the gas pockets

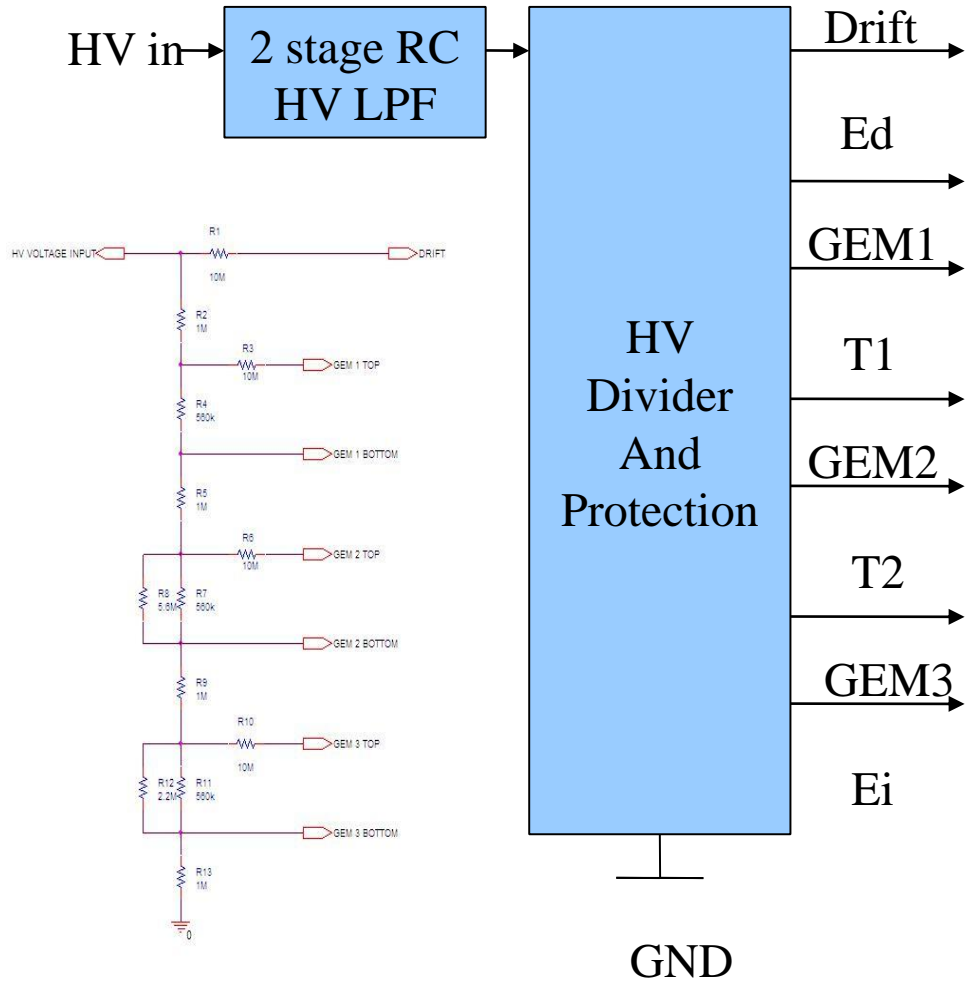


GE1/1 3D Model



GE1/1 - HV Divider

- GE1/1 – HV Divider has built in RC Filter
- The divider is made by HV SMD Resistors.



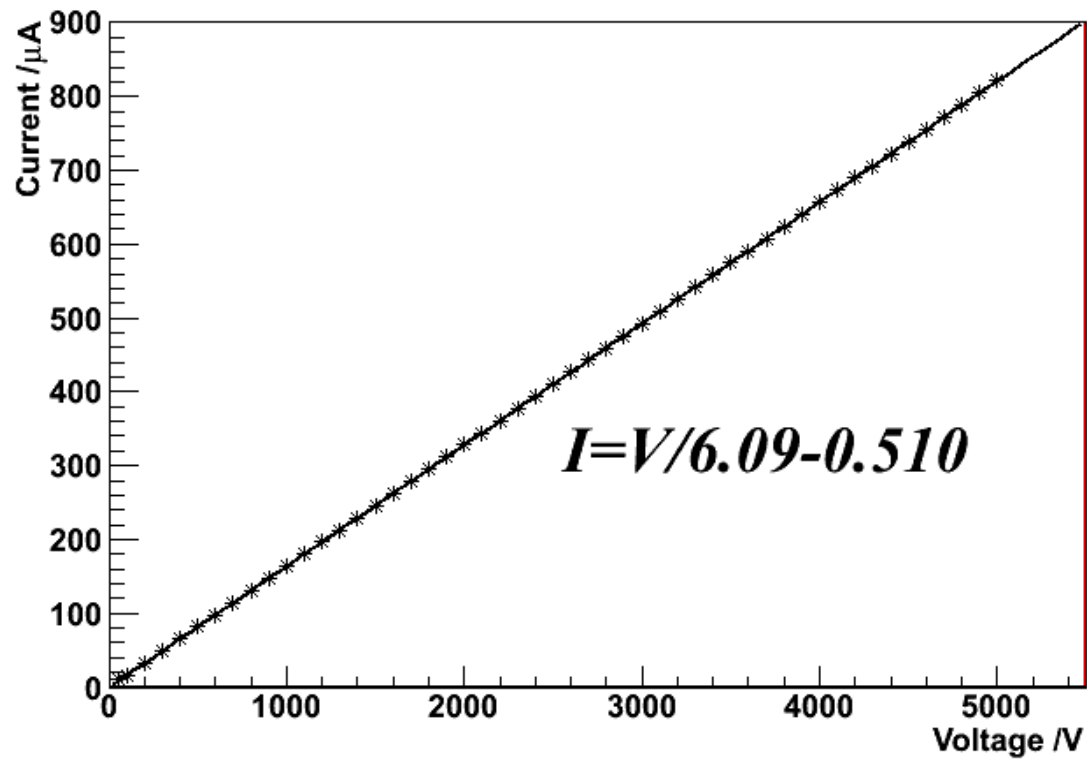
HV divider Production steps



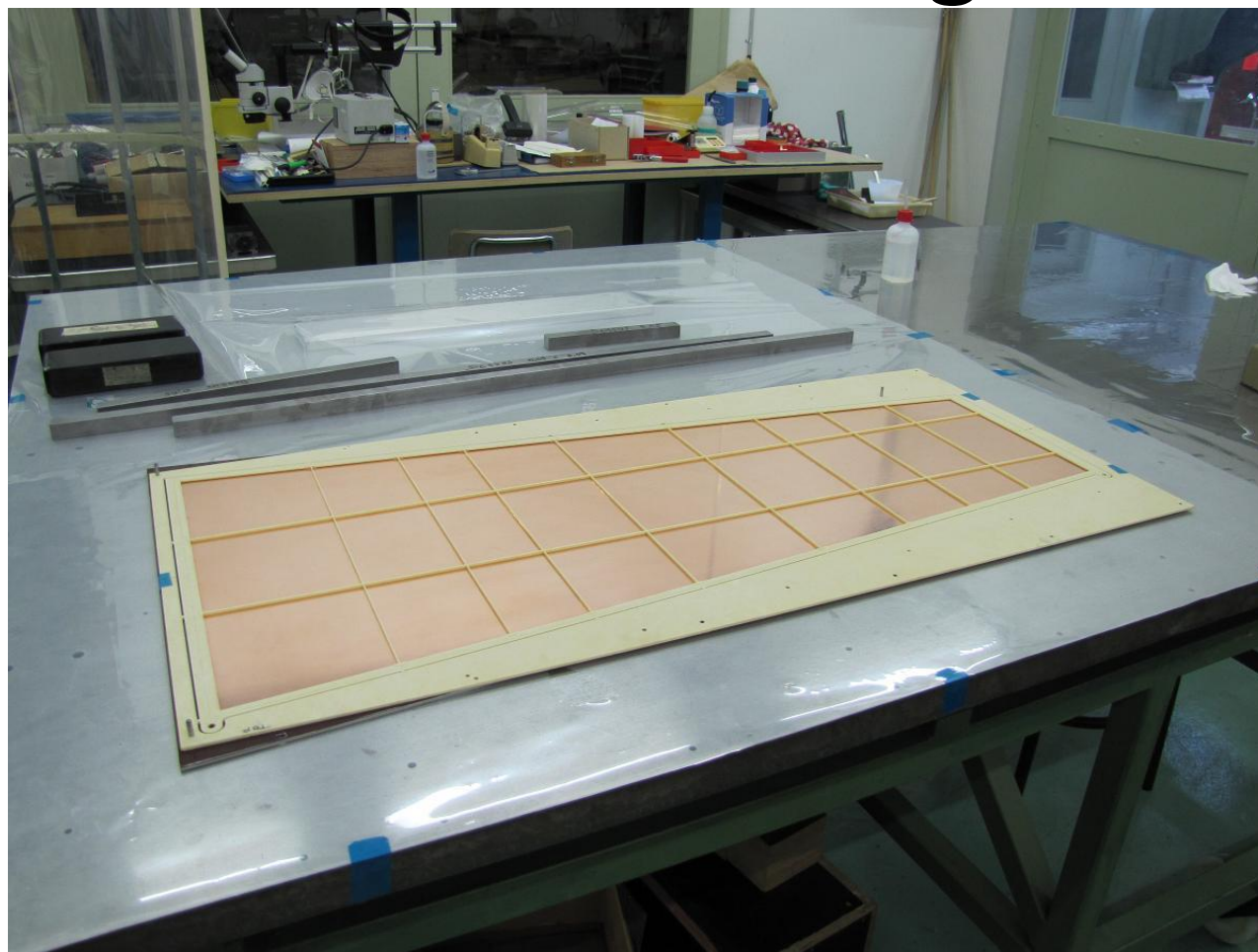
- PCB layout design is made with “Altium Designer” software
- 2 Layers PCB
- Deep cleaning after soldering the SMD components
- HV silicon protection layer for keeping the PCB fiberglass away from humidity

I/V measured plot

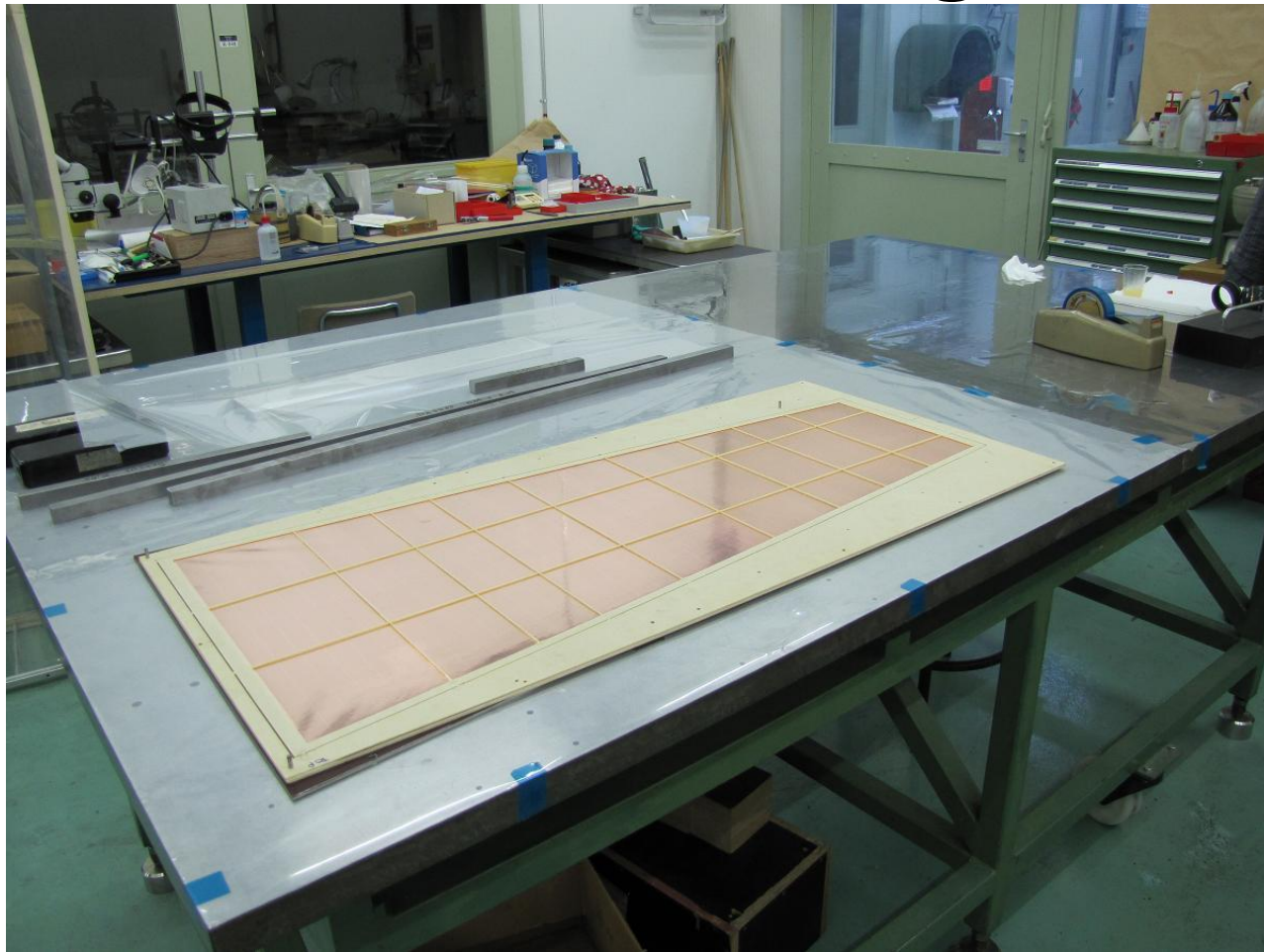
HV Divider I-V Test



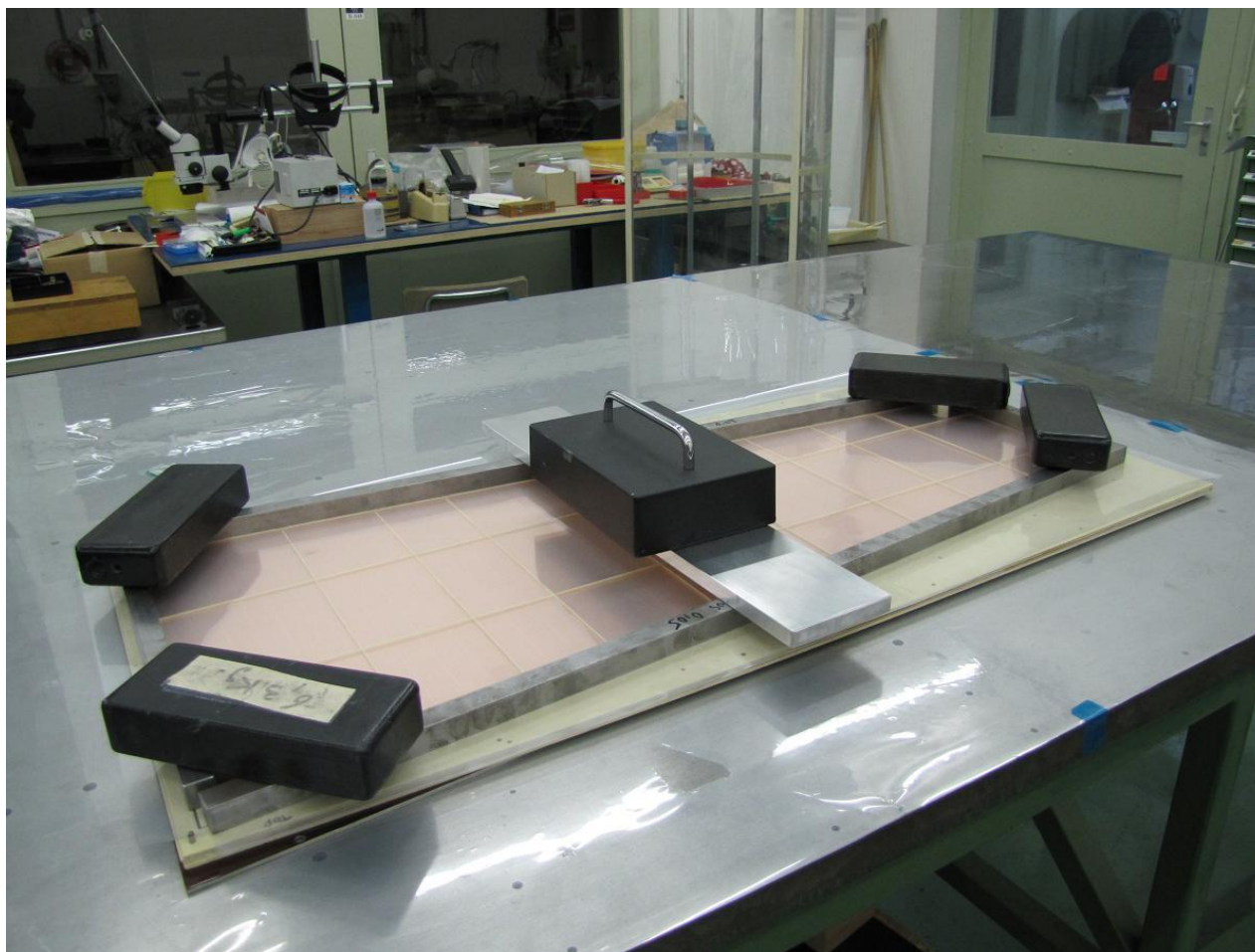
Glued drift and 3 gems



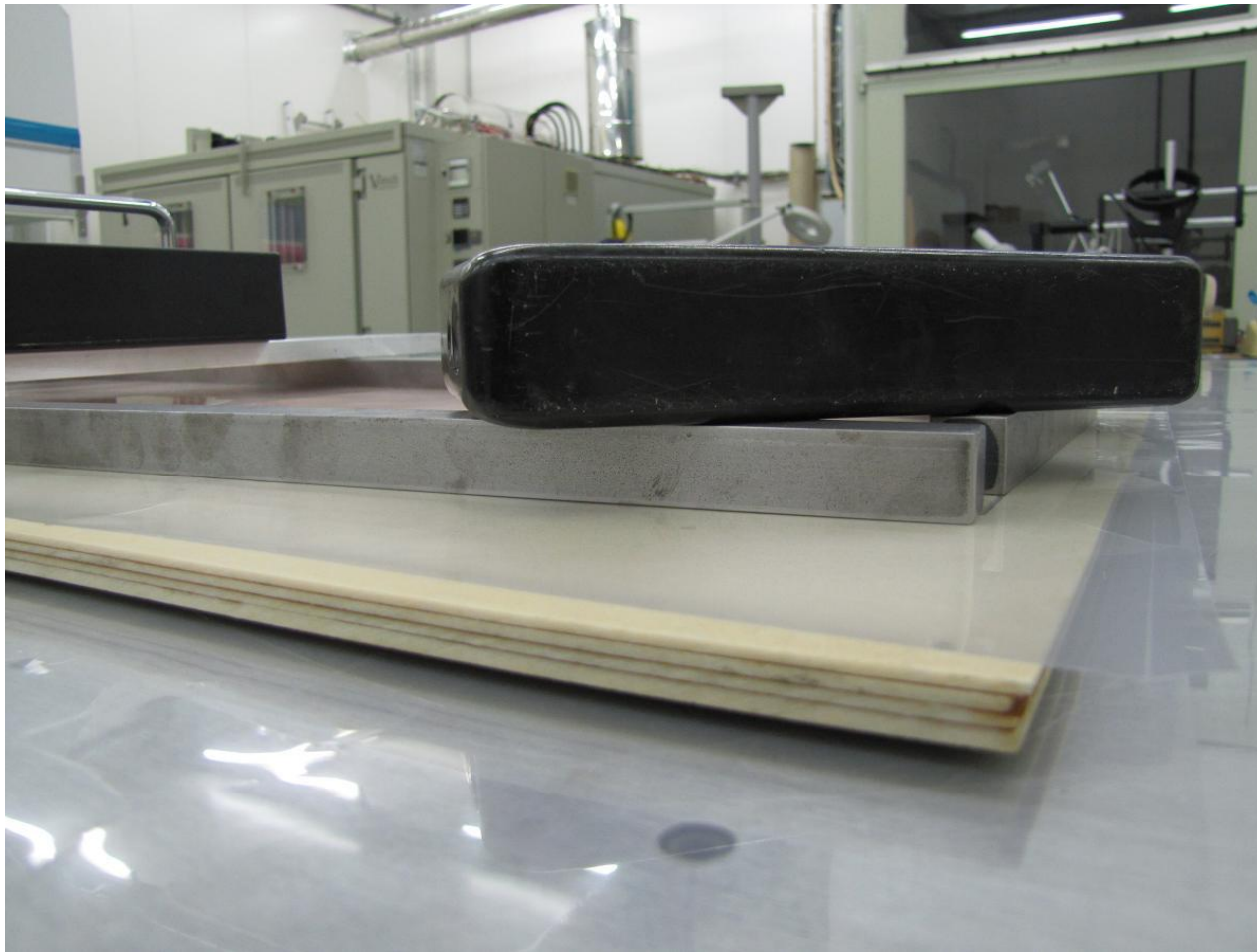
Glued drift and 3 gems



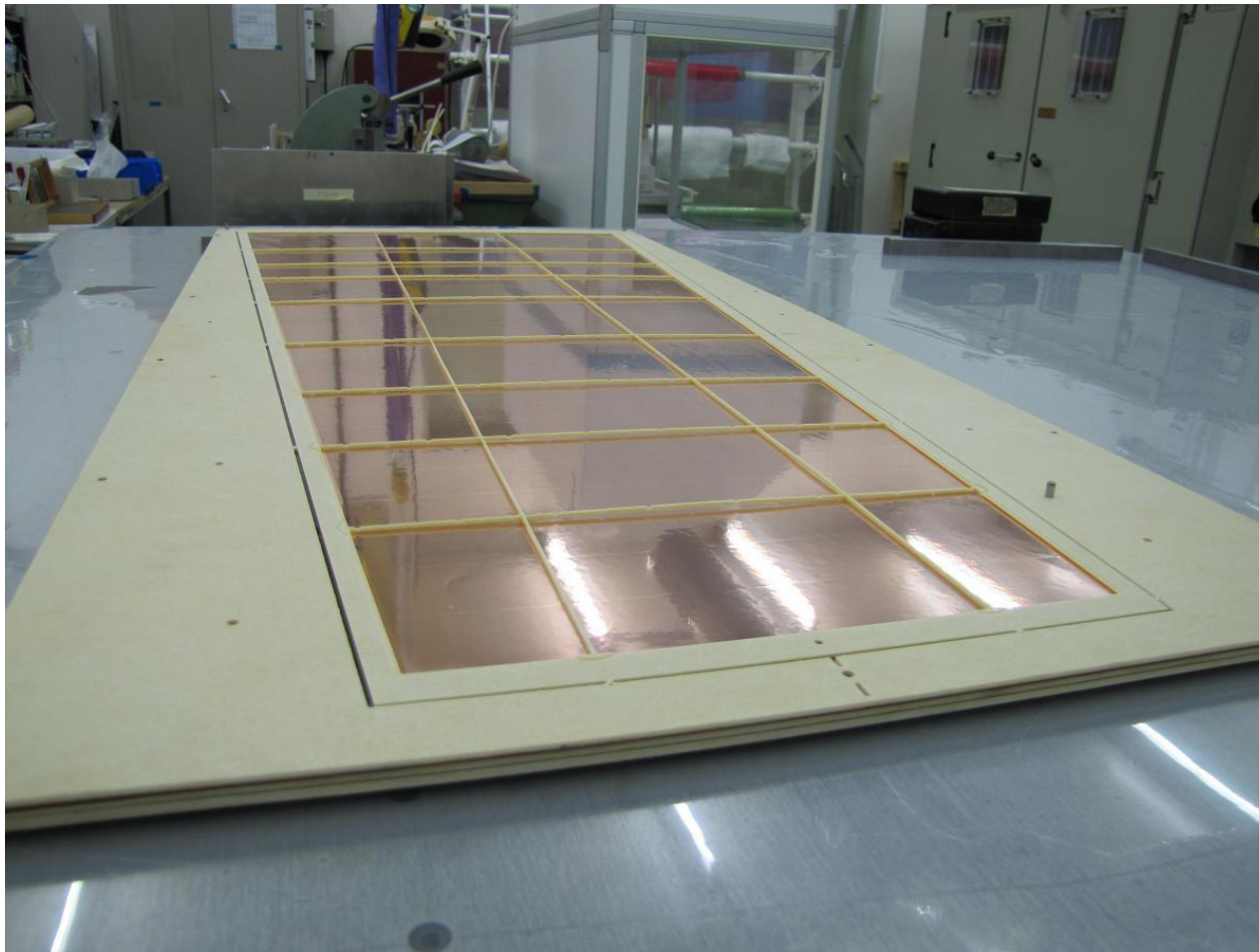
Weights on top



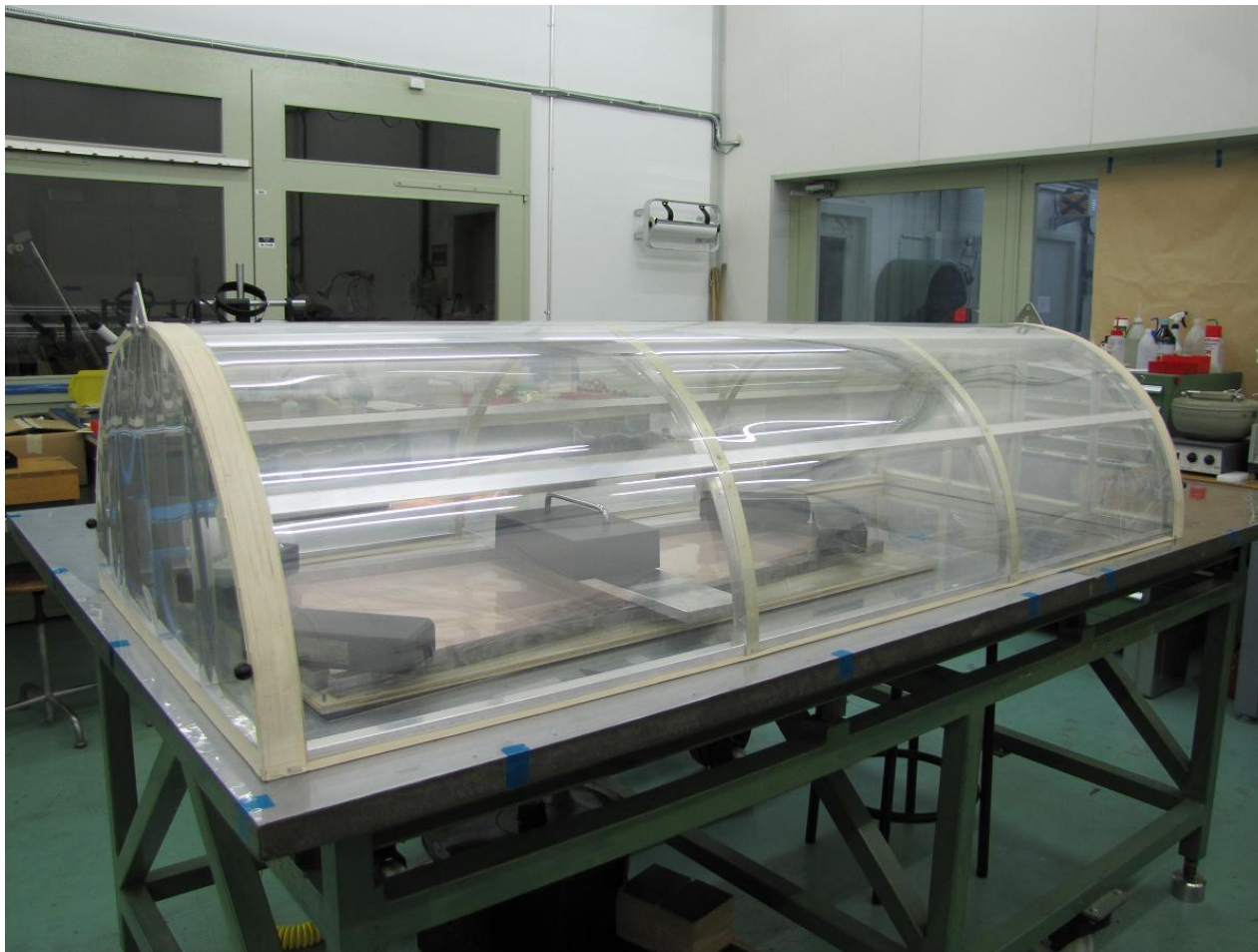
Corners



Without weights



Waiting the readout in safe



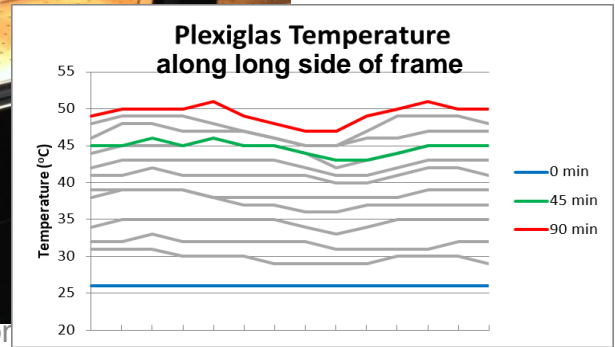
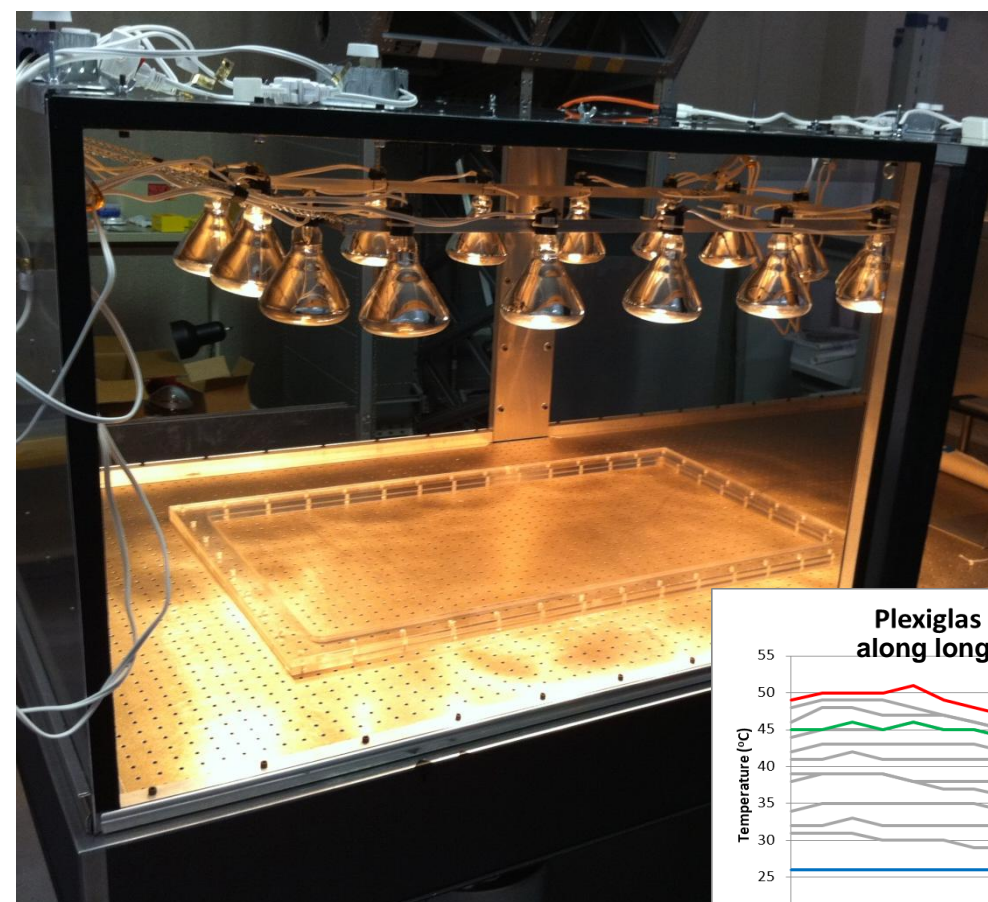
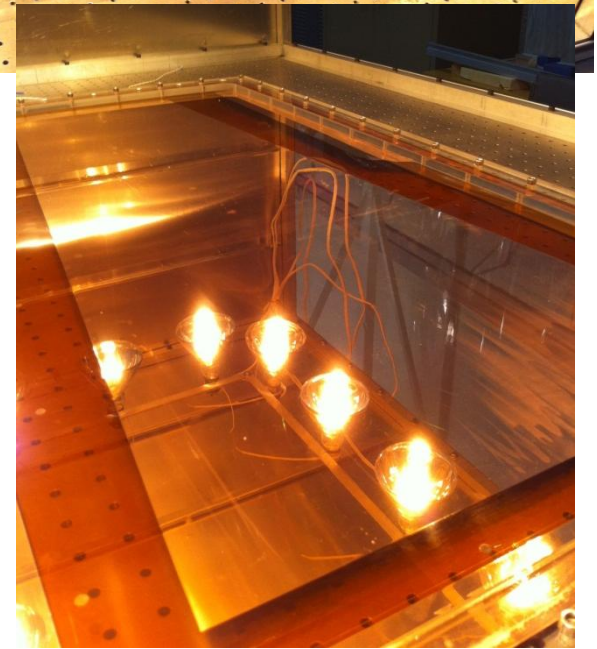
R&D at FIT FLORIDA

- CMS High- η upgrade

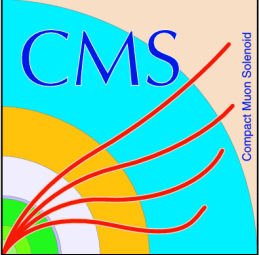
New, cost-effective GEM foil thermal stretching technique via **infrared heating** under clean room conditions in our high-bay lab (RD51 Technical Note in prep.)



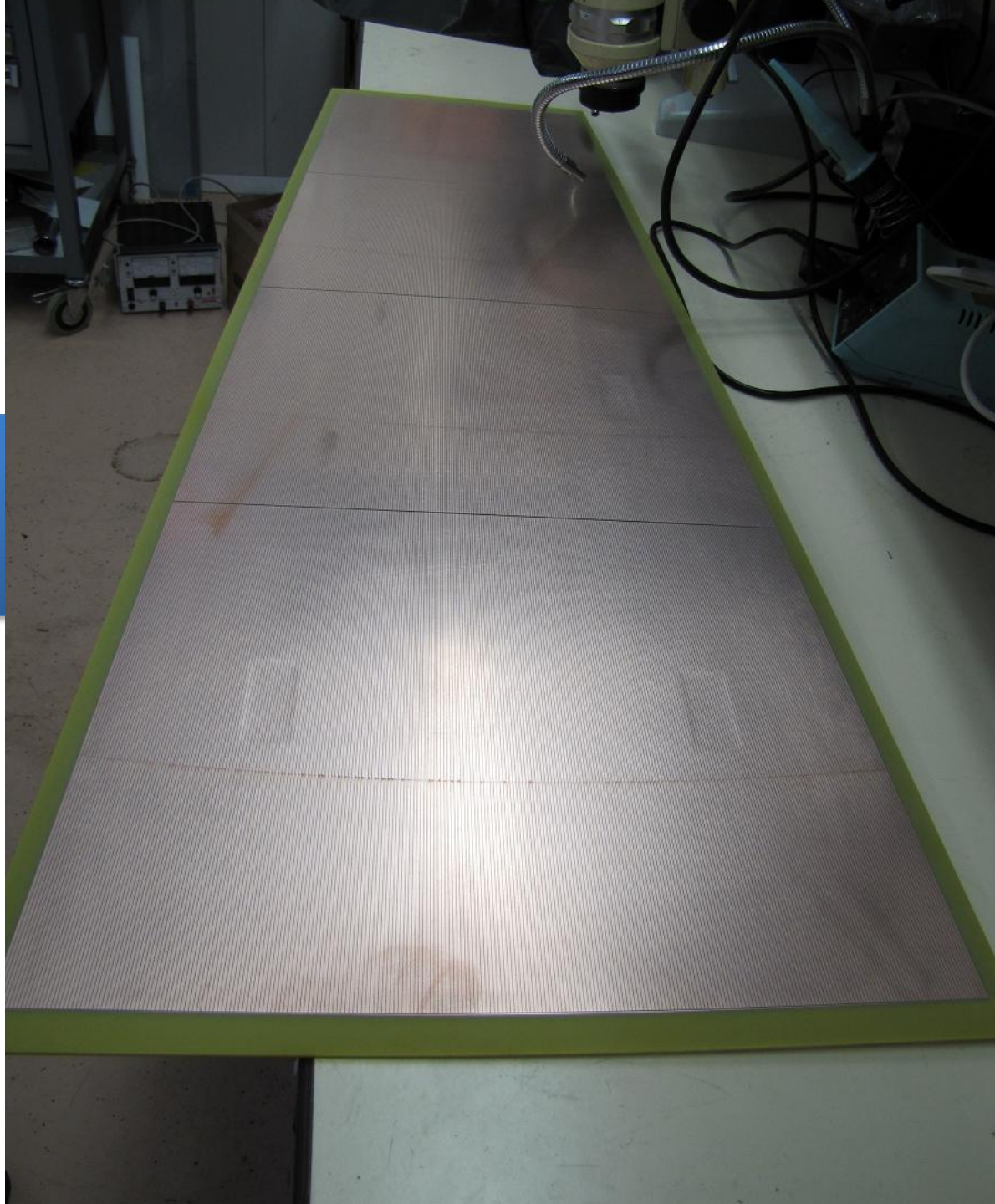
Works well!



Sep 30, 2010



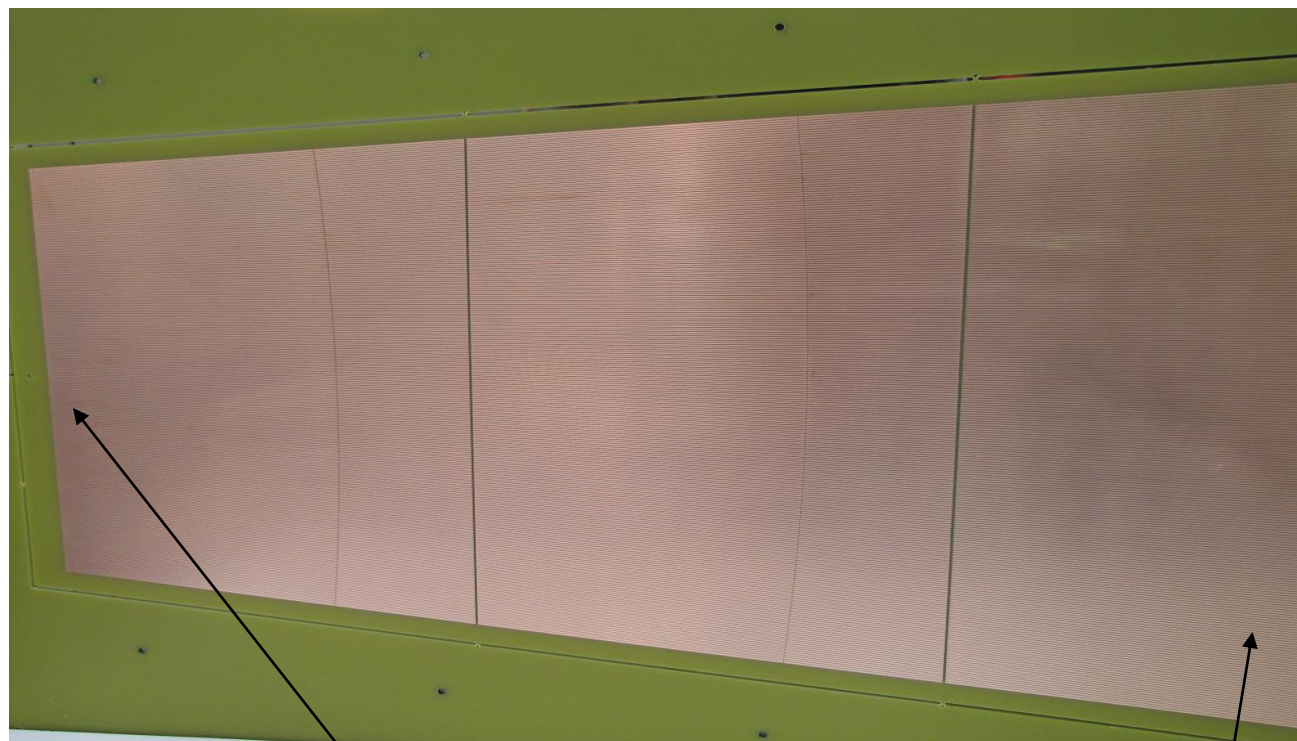
READOUT STUDIES



Readout PCB



128 channels per connector
256 strips for each eta partition

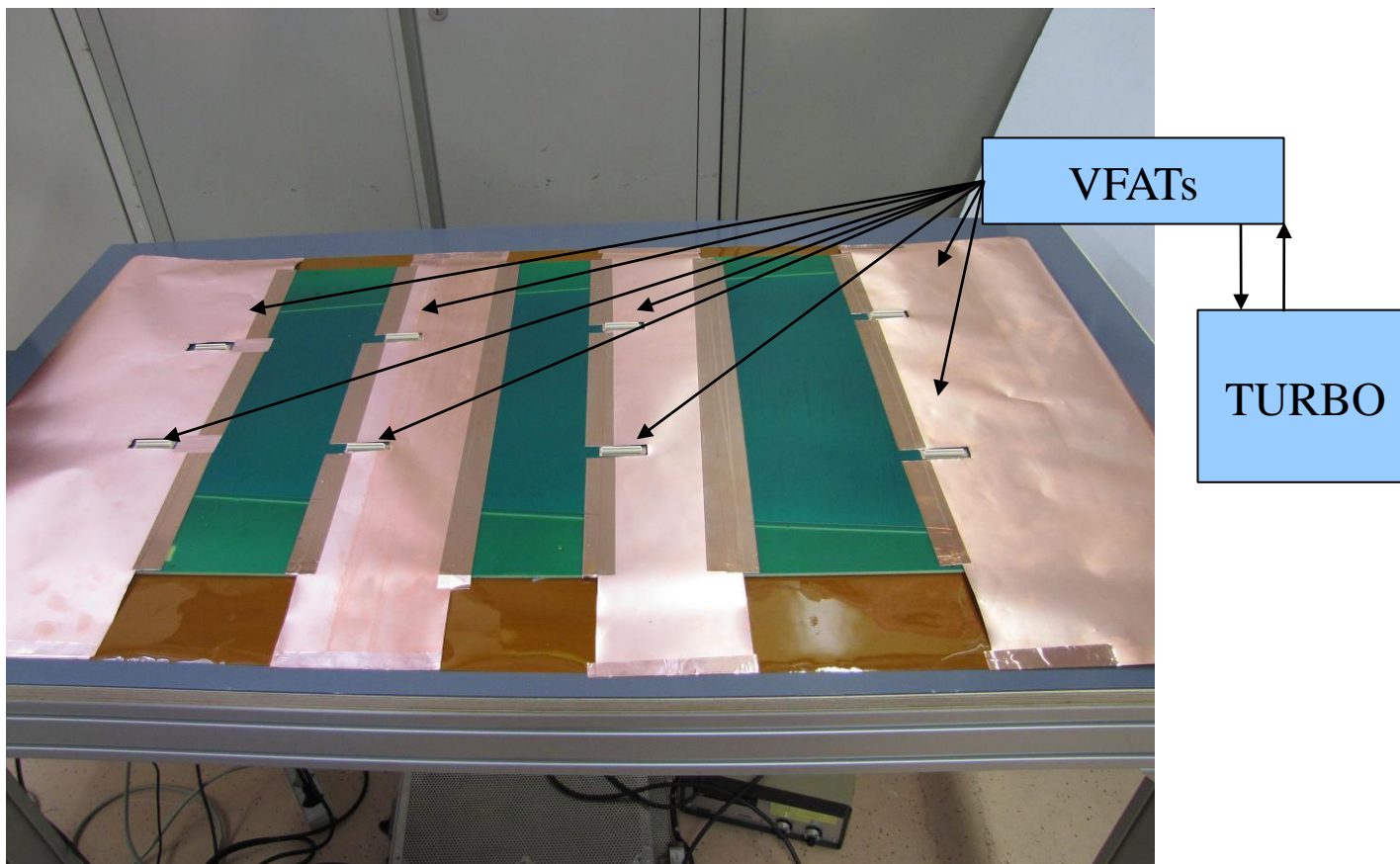


0.8mm pitch

1.6mm pitch

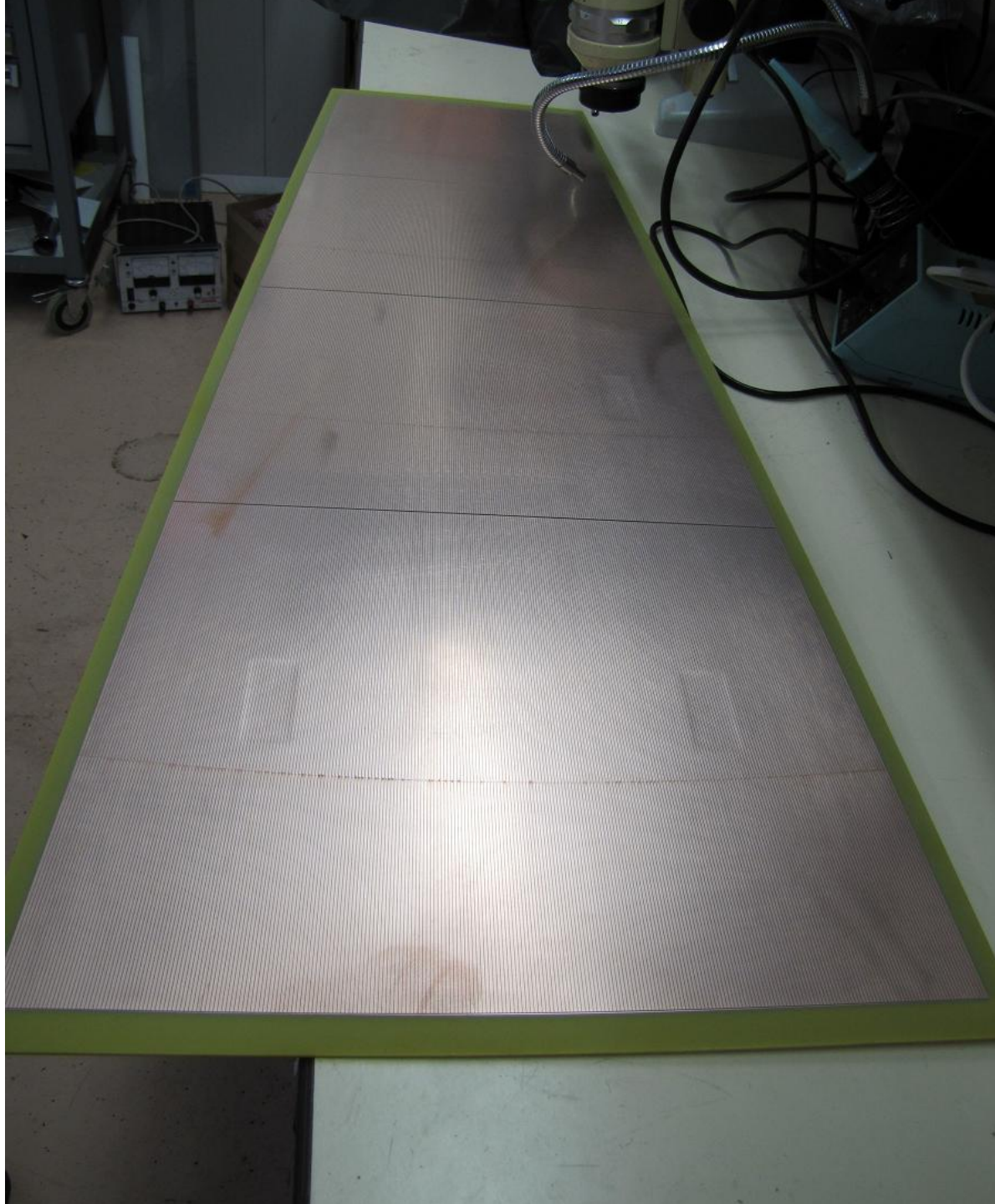
PCB thickness = 3mm

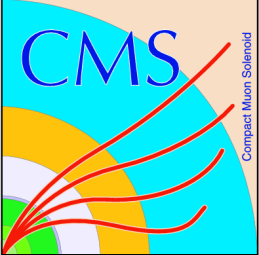
Readout Board Noise Test



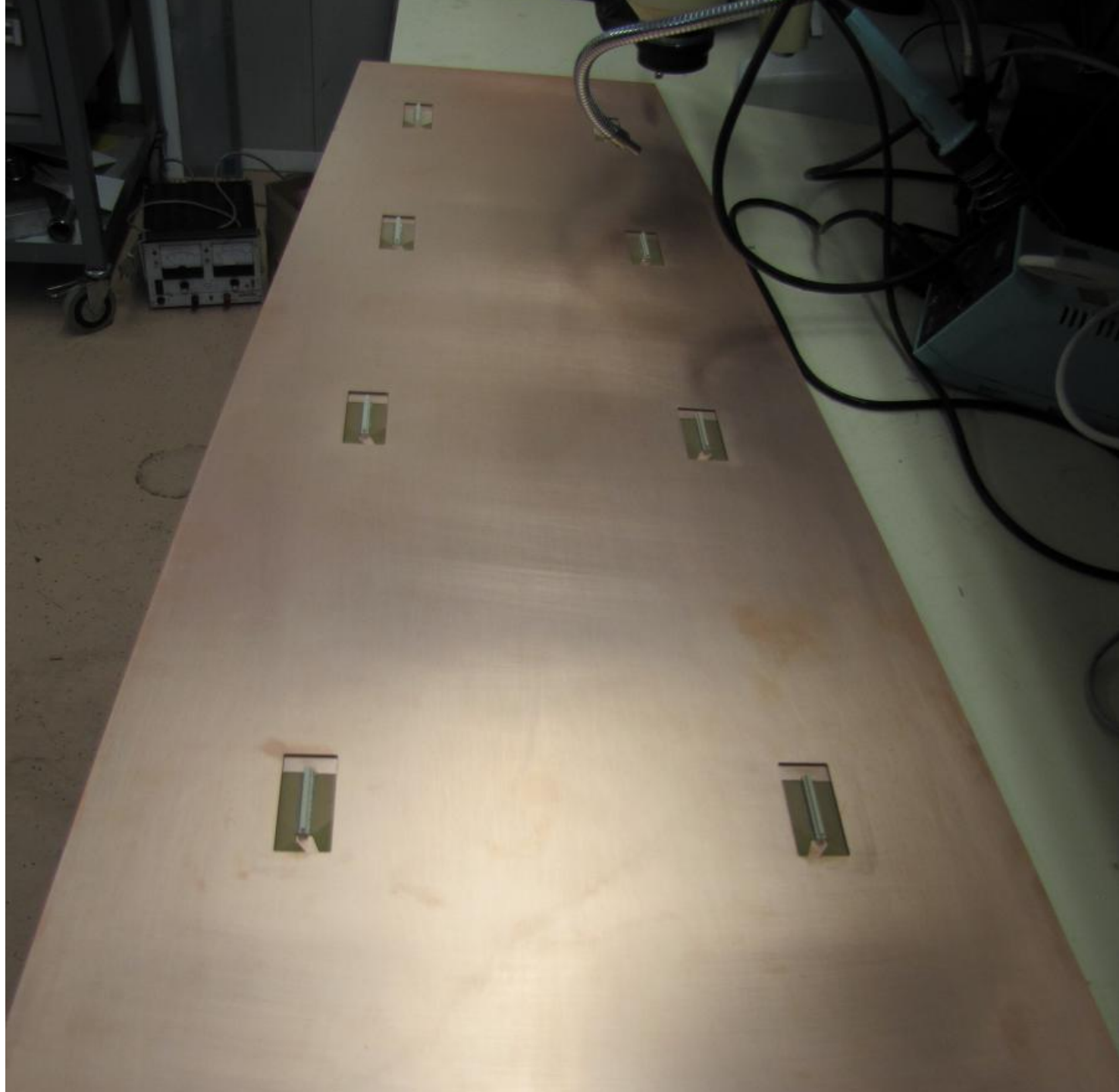
Noise test is ongoing with the VFAT electronics.

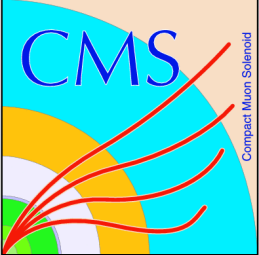
2 READOUT s tested
OLD No ground
plane
NEW - Ground
Plane layer integrated
between strip plane
and electronics





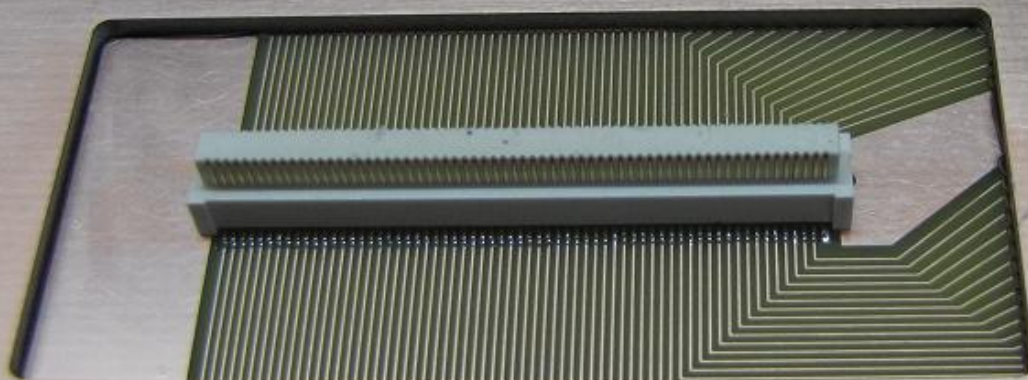
The new readout VFAT side

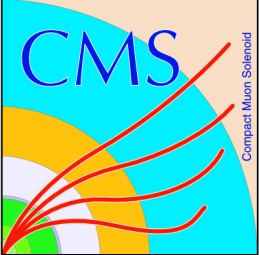




The new readout

VFAT slot



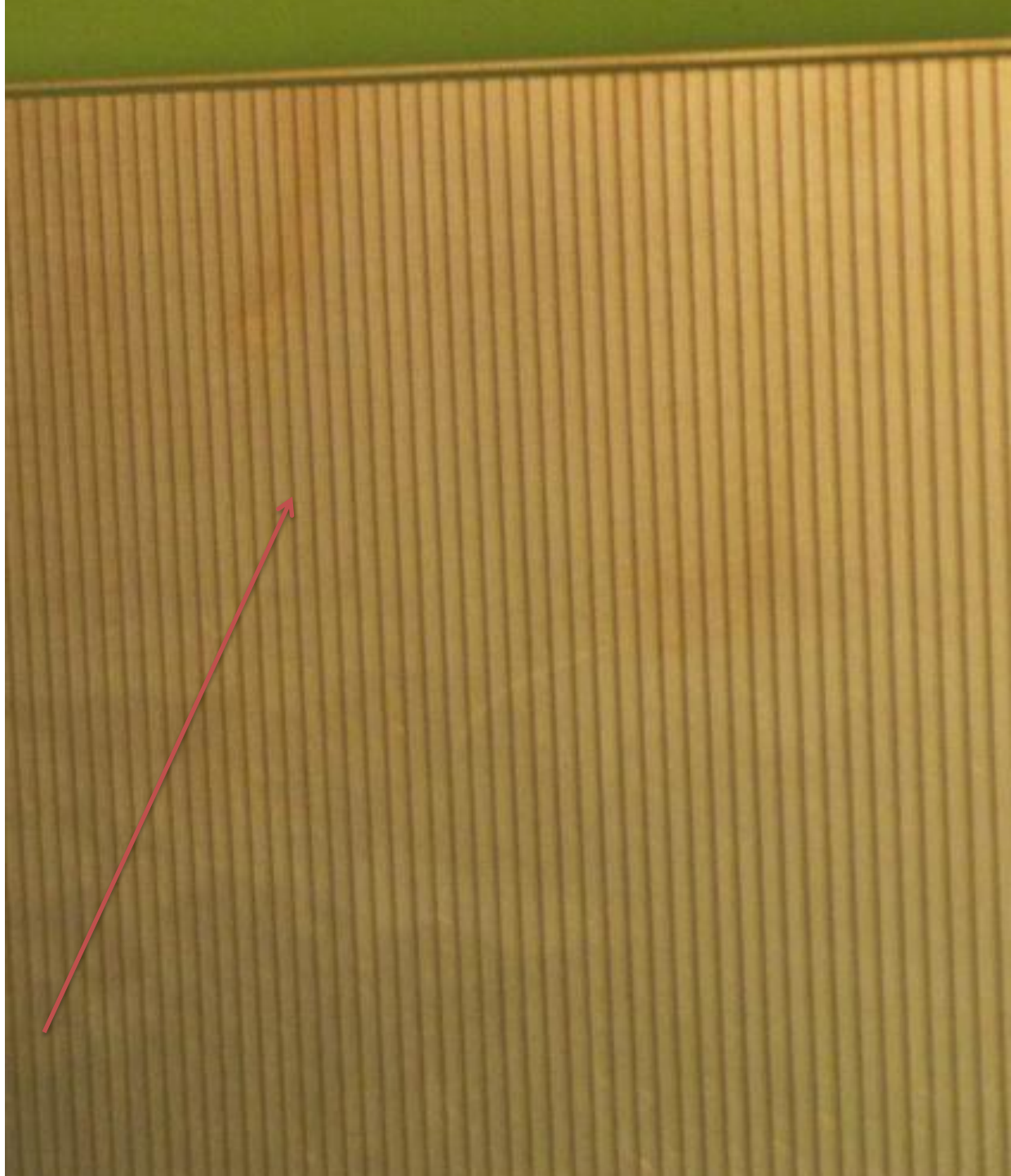


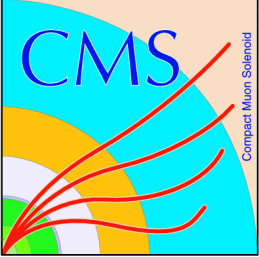
The new readout

1 defect is found

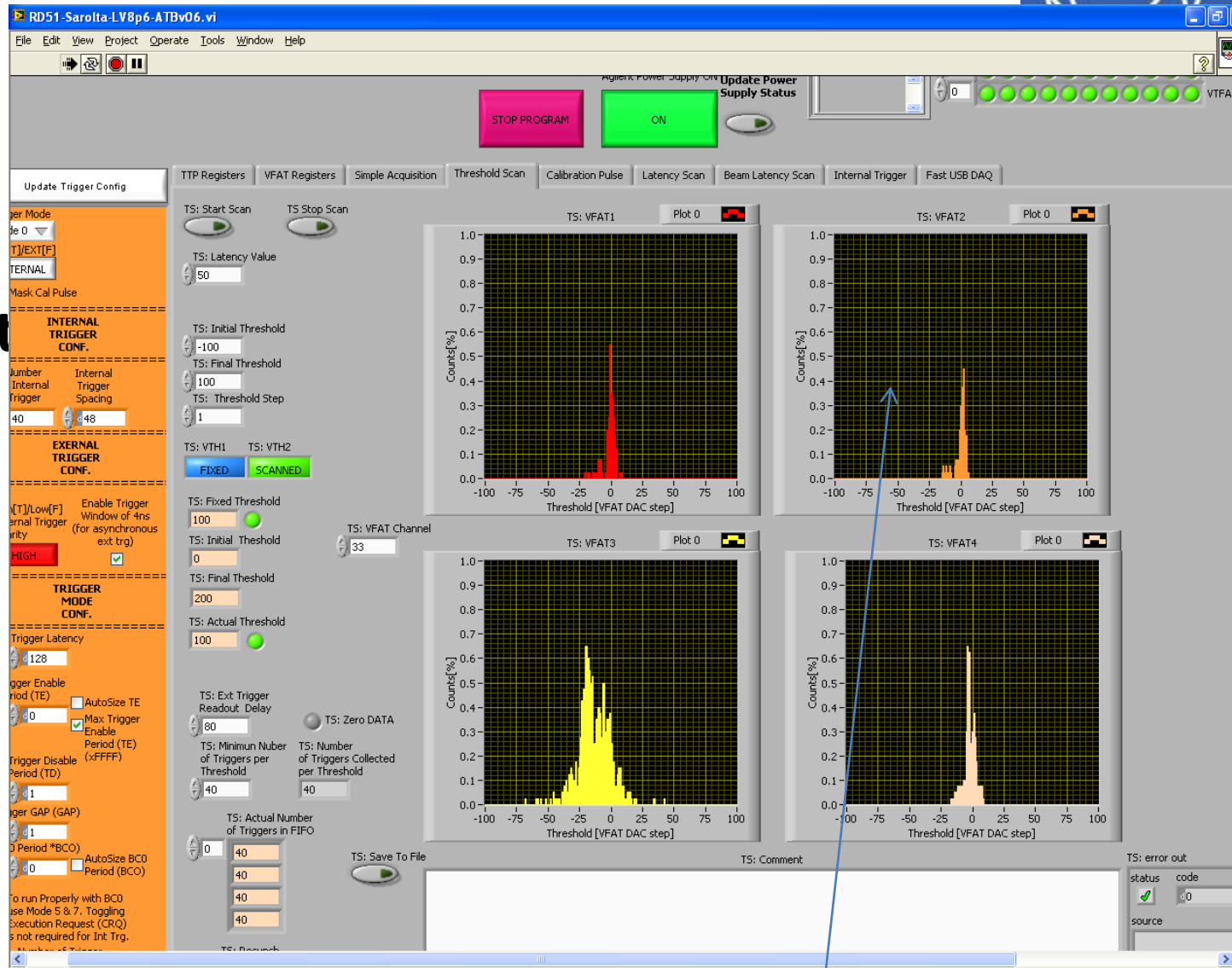
There is non etched copper in the low eta partition end. Due to this we have a floating copper area very close to our strips. It is source of noise.

Non etched copper.
– Source of noise





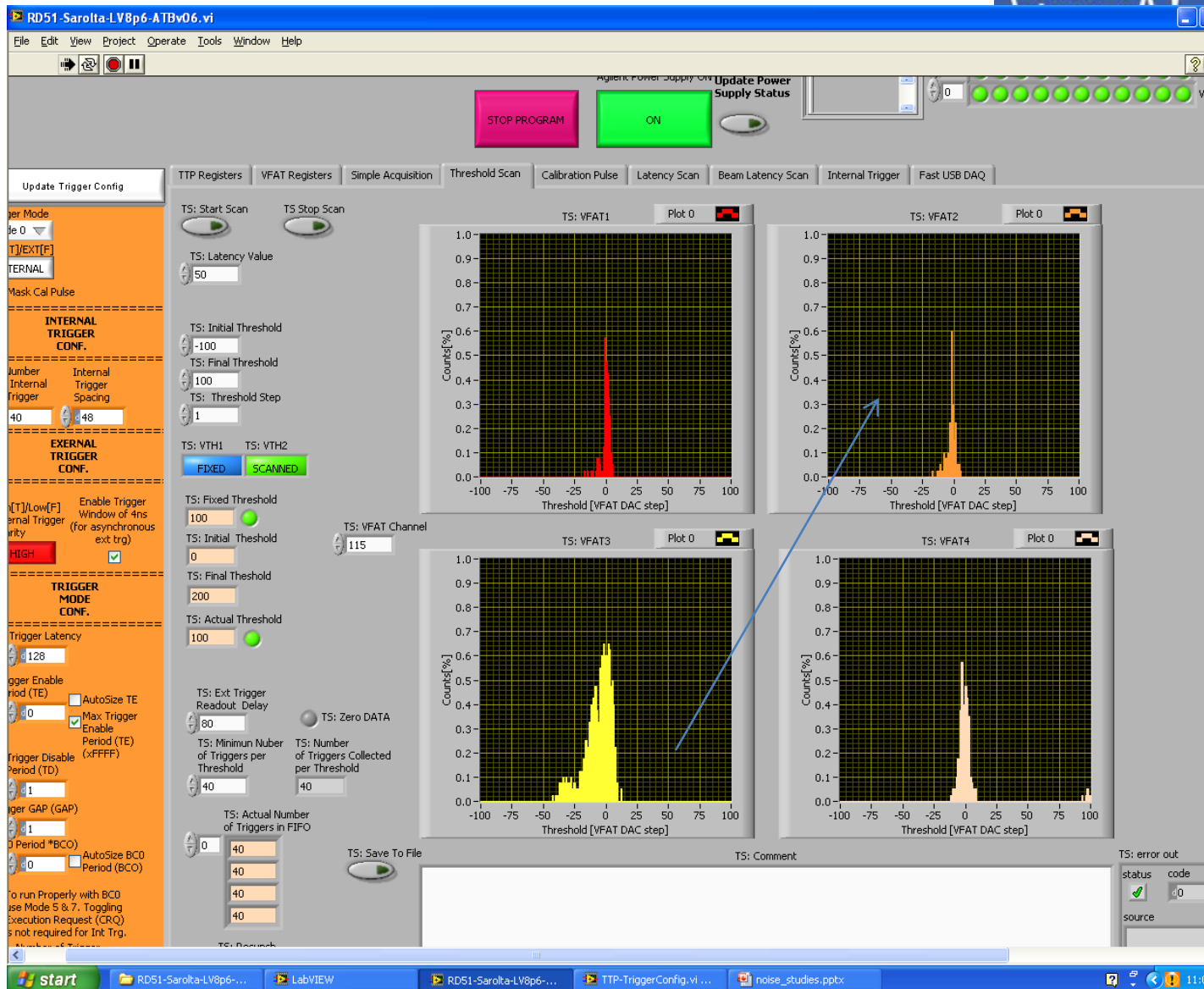
The old readout
We found
2 disconnected strips.
The noise level



The best noise level

New readout Noise level

Looks better then the old one.



The best noise level

GE1/1 Status and Plans

Item	Present Status
GEM foils production	Done
GEMs HV test	90% finished
Stretching and Framing procedure	90% finished
Drift Electrode	Done
HV divider production	In progress
HV divider test	Pending
Readout PCB production	Done
Readout PCB testing	In progress
Ready with prototype for 18.Oct.2010	OK